ISO808A, ISO808A-1

Datasheet

Galvanic isolated octal high-side power solid state relay with SPI interface for high inductive loads

PowerSO-36

TFQFPN32

Product status link
ISO808A
ISO808A-1

Product label
SUSTAINABLE TECHNOLOGY

Features

- $V_{CC(AMR)}$ = 45 V
- Wide process side op. range V_{CC} = 9.2 to 36 V
- R_{DS}(on) = 0.125 Ω per channel (TYP)
- Fast demagnetization of inductive loads $V_{DEMAG(TYP)}$ = V_{CC} - 54 V
- Per channel process side op. current
  - ISO808A/ISO808AQ I_{OUT} < 0.7 A
  - ISO808A-1/ISO808AQ-1 I_{OUT} < 1 A
- Low process and logic sides supply current
- Under-voltage shut down with auto restart and hysteresis
- Logic side 5 V and 3.3 V TTL/CMOS and MCU compatible I/Os
- Logic side SPI interface
- Common output enable/disable pin
- Reset function for IC outputs disable
- High common mode transient immunity
- Short circuit protection on output channels
  - ISO808A/ISO808AQ $I_{LIM(MIN)}$ = 0.7 A
  - ISO808A-1/ISO808AQ-1 $I_{LIM(MIN)}$ = 1 A
- Per-channel over-temperature protection with thermal independence of separate channels
- Case over-temperature protection
- Over-voltage protection (V_{CC} clamping)
- Loss of GND and V_{CC} protections
- Common fault open drain diagnostic
- V_{CC} Power Good open drain diagnostic for 24 V applications
- Designed to meet IEC 61000-4-2, IEC 61000- 4-4, IEC 61000-4-5 and IEC 61000-4-8
- UL1577 and UL508 certified
- PowerSO-36 and TFQFPN32 Package

Applications

- Programmable logic control
- Industrial PC peripheral input/output
- Numerical control machines
- Drivers for all type of loads (resistive, capacitive, inductive)

Description

The ISO808A, ISO808A-1 (PowerSO-36) and ISO808AQ, ISO808AQ-1 (TFQFPN32) are galvanic isolated 8-channel drivers featuring a low supply current. Each driver contains 2 independent galvanic isolated voltage domains (V_{CC} and V_{DD} for the Process and Control Logic stages, respectively). The ICs are intended for driving any kind of load with one side connected to ground.

The Control Logic Stage features an 8-bit Output Status Register (where the MCU sets the ON/OFF status of the output channels in the Process Stage), daisy chaining is allowed. The two stages communicate through the galvanic isolation channel by an ST proprietary protocol.

Active channel current limitation (OVL) combined with thermal shutdown (OVT), independent for each channel, protects the device against overload.

Built-in thermal shut down protects each channel from over-temperature and overload: each overheated channel automatically turns OFF after its junction temperature triggers the protection threshold (T_{JSD}). The channel turns back ON if its junction temperature decreases lower than restart threshold (T_{JR}).

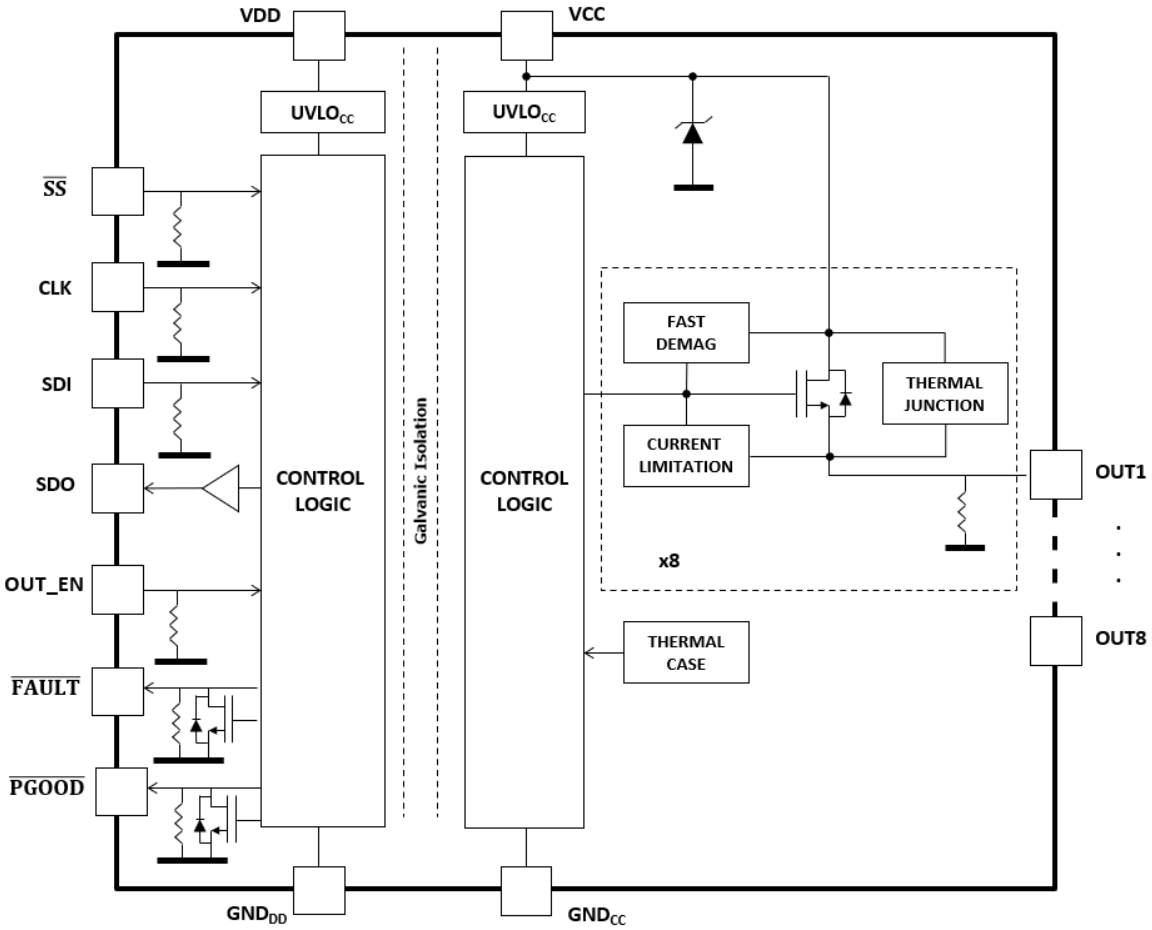
An additional case temperature sensor protects the whole chip against over-temperature (OVC event): if the case temperature triggers the T_{CSD} threshold then overloaded channels are turned OFF and will restart only when case temperature decreased down to the reset threshold (T_{CR}). Non overloaded channels continue to operate normally.

Other embedded functions are loss of ground protection, V_{CC} and V_{DD} UVLOs (with hysteresis), watchdog and V_{CC} Power GOOD.

An internal circuit provides an OR-wired not latched common $\overline{\text{FAULT}}$ indicator signaling the channel OVT. The $\overline{\text{PGOOD}}$ diagnostic pin is activated if V_{CC} goes below the power good threshold. Both $\overline{\text{FAULT}}$ and $\overline{\text{PGOOD}}$ pins are open drain, active low, fault indication pins.

1 Block diagram

Figure 1. **Block diagram**



2 Pin connection

Figure 2. **Pin connection PowerSO-36 (top through view)**

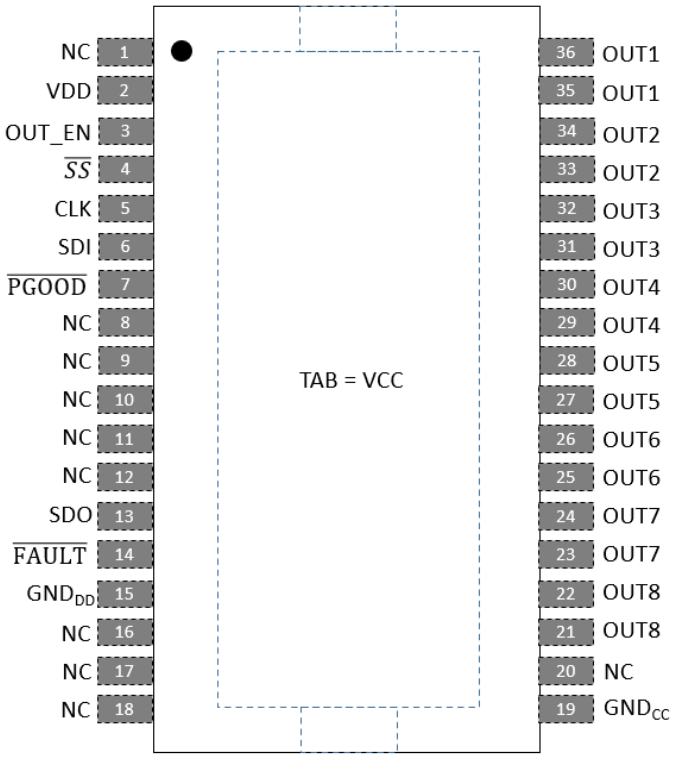


Figure 3. **Pin connection TFQFPN32 (top through view)**

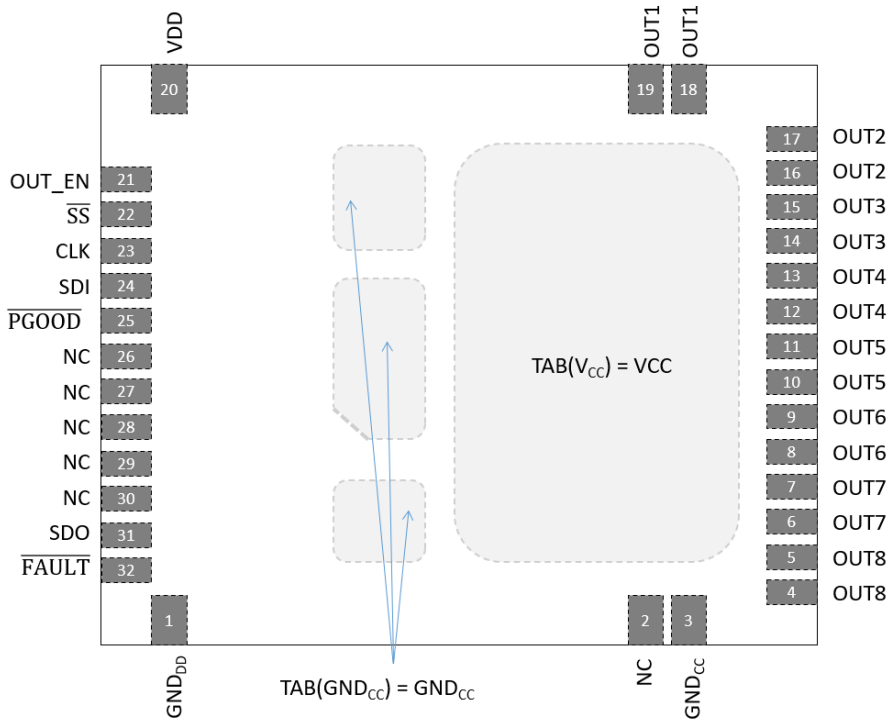


Table 1. Pin description

Pin		Name	Description
PowerSO-36	TFQFPN32		
1	-	N.C.	Not connected
2	20	V_{DD}	Positive Control Logic Stage supply
3	21	OUT_EN	Output enable
4	22	$\overline{SS}$	Chip select
5	23	CLK	Serial Clock Digital Input
6	24	SDI	SPI device Input (MOSI)
7	25	$\overline{PGOOD}$	Power Good diagnostic pin - active low
8	26	NC	Not connected
9	27	NC	Not connected
10	28	NC	Not connected
11	29	NC	Not connected
12	30	NC	Not connected
13	31	SDO	SPI device Output (MOSI)
14	32	$\overline{FAULT}$	Common fault (OVT and Communication Error) diagnostic pin - active low
15	1	GND_{DD}	Input logic ground, negative logic supply
16	-	NC	Not connected
17	-	NC	Not connected
18	2	NC	Not connected
19	3, TAB(GND_{CC})	GND_{CC}	Output power ground
20	-	NC	Not connected
21	4	OUT8	Channel 8 power output(1)
22	5		
23	6	OUT7	Channel 7 power output(1)
24	7		
25	8	OUT6	Channel 6 power output(1)
26	9		
27	10	OUT5	Channel 5 power output(1)
28	11		
29	12	OUT4	Channel 4 power output(1)
30	13		
31	14	OUT3	Channel 3 power output(1)
32	15		
33	16	OUT2	Channel 2 power output(1)
34	17		
35	18	OUT1	Channel 1 power output(1)
36	19		
TAB	TAB(V_{CC})	V_{CC}	Exposed tab internally connected to V_{CC} positive Process Stage supply voltage

1. *Connect the two pins on the same net of the application board*

3 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Min.	Max.	Unit
V_{CC}	Process Stage supply voltage	-0.3	+45	V
V_{DD}	Control Logic Stage supply voltage	-0.3	+6	V
V_{IN}	DC Input pins ($\overline{SS}$, CLK, SDI and OUT_EN) voltage	-0.3	V_{DD}	V
V_{SDO}	DC SDO pin voltage	-0.3	V_{DD}	V
V_{FAULT}, V_{PGOOD}	$\overline{FAULT}$ and $\overline{PGOOD}$ pins voltage	-0.3	+6.0	V
I_{GNDdd}	DC digital ground Reverse Current		-25	mA
I_{OUT}	Channel Output Current (continuous)		Internally limited	A
I_{GNDcc}	DC Power Ground Reverse Current		-250	mA
I_{RX}	Reverse Output Current (from OUTx pins to V_{CC})		-6 (1)	A
I_{IN}	DC Input pins ($\overline{SS}$, CLK, SDI and OUT_EN) current	-10	+10	mA
I_{FAULT}, I_{PGODD}	$\overline{FAULT}$ and $\overline{PGOOD}$ pins current	-10	+10	mA
V_{ESD}	Electrostatic discharge with Human Body Model (R = 1.5 KΩ; C = 100 pF)		2000	V
V_{IO}	Isolation DC voltage applied between GND_{DD} and GND_{CC} pins for PowerSO-36		180	V
	Isolation DC voltage applied between GND_{DD} and GND_{CC} pins for TFQFPN32		75	
EAS	Single pulse avalanche energy per channel, all channels driven simultaneously @T_{AMB}= 125 °C, I_{OUT} = 0.6 A (PowerSO-36)		2.11	J
	Single pulse avalanche energy per channel, all channels driven simultaneously @T_{AMB}= 125 °C, I_{OUT} = 0.6 A (TFQFPN32)		0.48	
P_{TOT}	Power dissipation		Internally limited (2)	W
T_J	Junction operating temperature		Internally limited (2)	°C
T_{STG}	Storage temperature		-40 to 150	°C

1. *this value is intended with each couple of OUTx pins shorted on the application board*
2. *Protection functions are intended to avoid IC damage in fault conditions and are not intended for continuous operation. Continuous or repetitive operation of protection functions may reduce the IC lifetime.*

4 Thermal data

Table 3. Thermal data

Symbol	Parameter	Max. value		Unit
		PowerSO-36	TFQFPN32	
$R_{th\ j\text{-}case}$	Thermal resistance, junction-to-case (1)	0.8	1	°C/W
$R_{th\ j\text{-}amb}$	Thermal resistance, junction-to-ambient (2)	16.9	25	

1. *Rth between the die and the bottom case surface measured by cold plate as per JESD51-12.*
2. *JESD51-7.*

5 Electrical characteristics

9.2 V ≤ V_{CC} ≤ 36 V; 2.75 V ≤ V_{DD} ≤ 5.5 V; -40 °C < T_J < 125 °C, unless otherwise specified.

Table 4. Power section

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC}	Operating voltage range		9.2		36	V
$V_{CC(THON)}$	V_{CC} undervoltage turn-on threshold	V_{DD} = 3.3 V, V_{CC} increasing		8.4	9.2	V
$V_{CC(THOFF)}$	V_{CC} undervoltage turn-off threshold	V_{DD} = 3.3 V, V_{CC} decreasing	7.7	8.1		V
$V_{CC(HYS)}$	V_{CC} undervoltage hysteresis			0.15		V
$V_{CCclamp}$	Clamp on VCC pin	I_{clamp} = 20 mA	47	52	57	V
$V_{CC(PGON)}$	V_{CC} Power Good turn-on threshold	V_{DD} = 3.3 V, VCC increasing		16.6	18.7	V
$V_{CC(PGOFF)}$	V_{CC} Power Good turn-off threshold	V_{DD} = 3.3 V, VCC decreasing	14.5	16.1		V
$V_{CC(PG-HYS)}$	V_{CC} Power Good hysteresis			0.5		V
$R_{DS(ON)}$	ON-state resistance (see Figure 4)	I_{OUT} = 0.5 A, T_J = 25 °C		0.125	0.16	Ω
		I_{OUT} = 0.5 A, T_J = 125 °C			0.26	
I_{CC}	Power supply current	All channels in OFF-state, V_{CC} = 36 V		5.5		mA
		All channels in ON-state, V_{CC} = 36 V		16		
I_{LGND}	Ground disconnection output current	V_{CC} = V_{GND} = 0 V V_{OUT} = -24 V			500	µA
$V_{OUT(OFF)}$	OFF-state output voltage	Channel OFF and I_{OUT} = 0 A			3	V
$I_{OUT(OFF)}$	OFF-state output current	Channel OFF and V_{OUT} = 0 V			5	µA

Table 5. Digital supply voltage

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{DD}	Operating voltage range		2.75		5.5	V
$V_{DD(THON)}$	V_{DD} undervoltage turn-on threshold	V_{CC} = 24 V, V_{DD} increasing	2.55		2.75	V
$V_{DD(THOFF)}$	V_{DD} undervoltage turn-off threshold	V_{CC} = 24 V, V_{DD} decreasing	2.45		2.65	V
$V_{DD(HYS)}$	V_{DD} undervoltage hysteresis		0.04	0.1		V
I_{DD}	V_{DD} supply current	V_{DD} = 5 V and SPI not transmitting		4.5	6	mA
		V_{DD} = 3.3 V and SPI not transmitting		4.4	5.9	mA

Table 6. Diagnostic pin and output protection function

Symbol	Parameter		Test conditions	Min.	Typ.	Max.	Unit
V_{FAULT}	$\overline{FAULT}$ pin open drain voltage output low		I_{FAULT} = 5 mA			0.4	V
I_{LFAULT}	$\overline{FAULT}$ output leakage current		V_{FAULT} = 5 V			1	µA
V_{PGOOD}	$\overline{PGOOD}$ pin open drain voltage output low		I_{PGOOD} = 5 mA			0.4	V
I_{LPGOOD}	$\overline{PGOOD}$ output leakage current		V_{PGOOD} = 5 V			1	µA
I_{PEAK}	Maximum DC output current before limitation		V_{CC} = 24 V; R_{LOAD} = 0 Ω			2.3	A
I_{LIM}	Short-circuit current limitation	ISO808A, ISO808AQ		0.7		1.9	A
		ISO808A-1, ISO808AQ-1		1			
Hyst	I_{LIM} tracking limits				0.3		A
T_{JSD}	Junction shutdown temperature			150	175	200	°C
T_{JR}	Junction reset temperature				150		°C
T_{JHYST}	Junction thermal hysteresis				15		°C
T_{CSD}	Case shutdown temperature			125	130	135	°C
T_{CR}	Case reset temperature				115		°C
T_{CHYST}	Case thermal hysteresis				15		°C
V_{DEMAG}	Output voltage at turn-off		I_{OUT} = 0.5 A; I_{LOAD} >= 1 mH	V_{CC}-50	V_{CC}-54	V_{CC}-58	V

Table 7. Power switching characteristics (V_{CC} = 24 V; R_{LOAD} = 48 Ω; -40 °C < T_J < 125 °C)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
dV/dt(ON)	Turn-on voltage slope	(see Figure 5)		0.7		V/µs
tr	Rise time			19	32	µs
dV/dt(OFF)	Turn-off voltage slope			1.5		V/µs
tf	Fall time			7	23	µs
td(ON)	Turn-ON delay time	(see Figure 6)		15	24	µs
td(OFF)	Turn-OFF delay time			43	80	µs
$t_{w(OUT\_EN)}$	OUT_EN pulse width	(see Figure 11, Figure 12)	150			ns
$t_{p(OUT\_EN)}$	OUT_EN propagation delay			40	80	µs

Figure 4. $R_{DS(on)}$ measurement

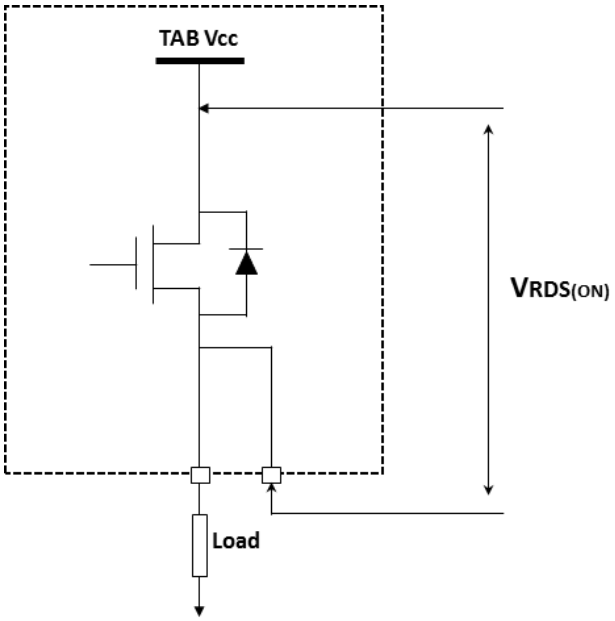


Figure 5. dV/dT definition

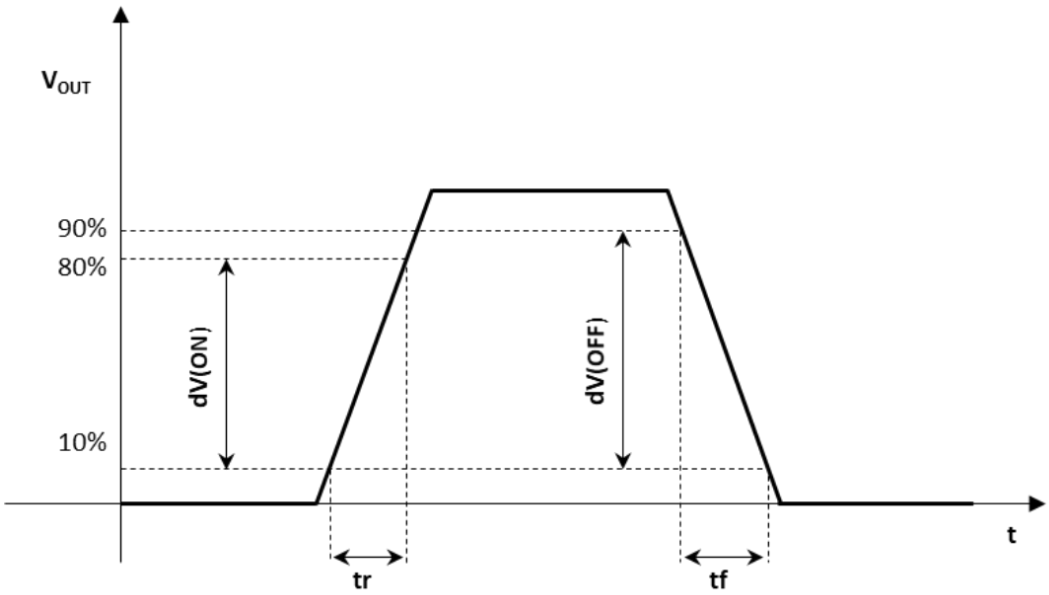


Figure 6. td(ON)-td(OFF) definition

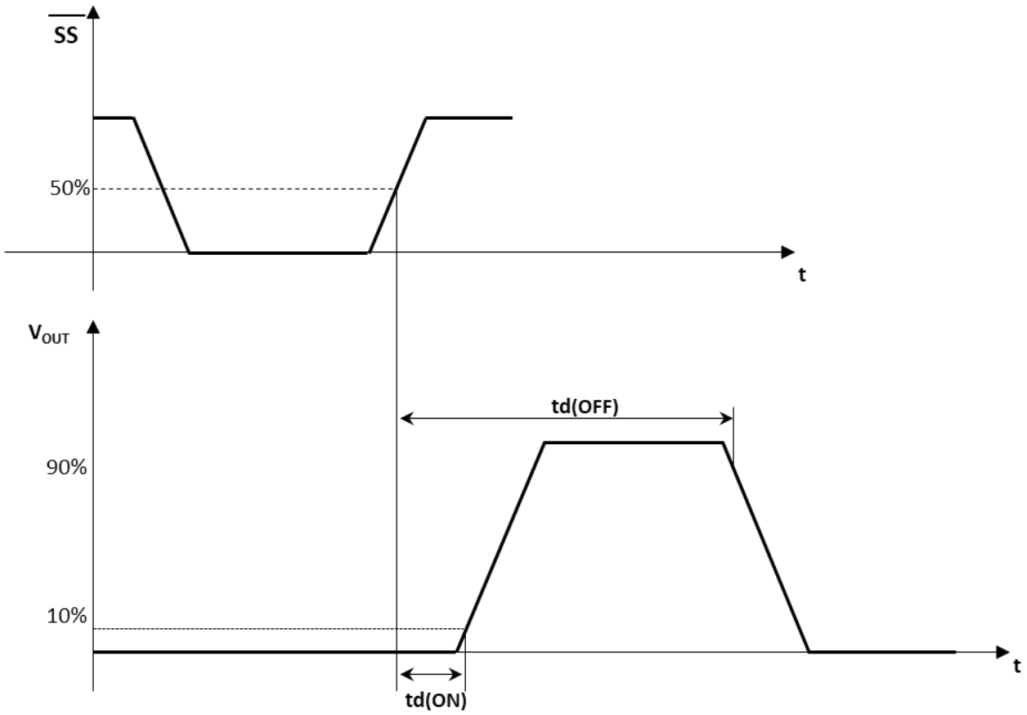


Table 8. Logic inputs and output

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IL}	$\overline{SS}$, CLK, SDI and OUT_EN low level voltage		-0.3		0.3 x V_{DD}	V
V_{IH}	$\overline{SS}$, CLK, SDI and OUT_EN high level voltage		0.7 x V_{DD}		V_{DD} +0.3	V
$V_{I(HYST)}$	$\overline{SS}$, CLK, SDI and OUT_EN hysteresis	V_{DD} = 5 V		100		mV
I_{IN}	$\overline{SS}$, CLK, SDI and OUT_EN current	V_{IN} = 5 V	10	55	90	µA
V_{SDOH}	SDO high level voltage	I_{SDO} = -1 mA	V_{DD}-0.2			V
V_{SDOL}	SDO low level voltage	I_{SDO} = +2 mA			0.2	V

Table 9. Serial interface timings (V_{DD} = 5 V; V_{CC} = 24 V; -40 °C < T_J < 125 °C)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
f_{CLK}	SPI clock frequency				20	MHz
T_{CLK}	SPI clock period		50			ns
tr(CLK) tf(CLK)	SPI clock rise/fall time (see Figure 8, Figure 9)				5	ns
tsu(SS)	SS setup time (see Figure 8, Figure 9)		80			ns
th(SS)	SS hold time (see Figure 8, Figure 9)		80			ns
tc(SS)	SS disable time (see Figure 8, Figure 9)		20			µs
tw(CLK)	CLK high time (see Figure 8, Figure 9)		15			ns
tsu(SDI)	Data input setup time (see Figure 8, Figure 9)		6			ns
th(SDI)	Data input hold time (see Figure 8, Figure 9)		6			ns
ta(SDO)	Data output access time (see Figure 8, Figure 9)	$R_{PULL-DOWN}$ = 300 Ω C_{LOAD} = 50 pF			25	ns
tdis(SDO)	Data output disable time (see Figure 8, Figure 9)				20	ns
tv(SDO)	Data output valid time (see Figure 8, Figure 9)				20	ns
t_{JITTER}	Jitter on single channel $t_{CYCLE\ (\ SS)}$ = 20 µs				6	µs
	Jitter on single channel $t_{CYCLE\ (\ SS)}$ < 20 µs				20	

Table 10. Internal communication timings (V_{DD} = 5 V; V_{CC} = 24 V; -40 °C < T_J < 125 °C)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$f_{refresh}$	Refresh delay			15		kHz
t_{WD}	Watchdog time		272	320	400	µs

Table 11. Insulation and safety-related specifications

Symbol	Parameter	Test conditions	Value		Unit
			PowerSO36	TFQFPN32	
CLR(1)	Clearance (minimum external air gap)	Measured from input terminals to output terminals, shortest distance through air	2.6	3.3	mm
CPG(1)	Creepage (minimum external tracking)	Measured from input terminals to output terminals, shortest distance path along body	2.6	3.3	mm
CTI(2)	Comparative tracking index (tracking resistance)		≥400	≥600	V
	Isolation group	Material group	II	I	-

1. *Creepage and clearance requirements should be applied according to the specific equipment isolation standard of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the PCB do not reduce this distance.*
2. *When high voltage is applied across the isolator, electric discharges on or close to the surface of the package, can cause localized deterioration in the mold compound, resulting in a partially conducting path from one side of the isolator to the other. This phenomenon is called tracking. The ability of a material to withstand tracking is quantified by a comparative tracking index (CTI). Using a mold compound with a higher CTI allows the use of smaller packages and saves board space.*

Table 12. Insulation characteristics

Symbol	Parameter	Test condition	Value		Unit
			PowerSO36	TFQFPN32	
In accordance with IEC 60747-17					
V_{PR}	Input-to-output test voltage	Method a, type test, tm = 10 s partial discharge < 5 pC	1500	1500	V_{PEAK}
		Method b, 100% production test, tm = 1 s partial discharge < 5 pC	1758	1758	V_{PEAK}
V_{IOTM}	Transient overvoltage	Type test; t_{ini} = 60 s	3537	4245	V_{PEAK}
V_{IOSM}	Maximum surge insulation voltage	Type test	3537	4245	V_{PEAK}
R_{IO}	Insulation resistance	Type test V_{IO} = 500 V, T_{STG} = 60 s	$>10^9$	$>10^9$	Ω
UL1577					
V_{ISO}	Insulation withstand voltage	1 min. type test	2000/2830	2500/3536	V_{RMS}/V_{PEAK}
V_{ISO} test	Insulation withstand test	1 s 100% production	2500/3537	3000/4245	V_{RMS}/V_{PEAK}
Common Mode Transient Immunity					
dV_{ISO}/dt	CMTI	Type test at V_{CM} = 500 V	±25	±25	V/ns

Table 13. Safety limits

Symbol	Parameter	Test conditions	Value	Unit
Input safety, Logic side				
T_{SI}	Safety temperature of Logic side	-	150	°C
P_{SI}	Safety power of Logic side(1)	V_{DD} ≤ 6.0 V, $V_{LOGIC(x)}$ ≤ 6.0 V, $I_{LOGIC(x)}$ ≤ 10 mA, T_J ≤ T_{SI}	0.9	W
Output safety, Process side				
T_{SO}	Safety temperature of Process side	-	150	°C
P_{SO}	Safety power of Process side(1)	V_{CC} ≤ 36 V, $I_{OUT(x)}$ ≤ 1.5 A, T_J ≤ T_{SO}	5	W

1. *Respecting the above limits prevents potential damage to the isolation barrier upon failure on logic or process side circuitry. The user should apply these values to protect the IC and ensure the safety of the embedded isolation barrier. LOGIC(x) stands for any pin on the logic side; OUT(x) stands for any of the 8 output pins on the process side.*

6 Functional description

6.1 Serial interface

An integrated SPI peripheral provides a fast communication interface between an external micro-controller and the IC purposing to drive ON/OFF the Power Stage outputs. Daisy chaining is allowed.

It follows the timing requirement established by the synchronous serial communication standard and works up to 20 MHz communication speed.

The communication implemented expects 8-bit data communication; the frame sent by the micro-controller only contains the status of the channels (ON or OFF), while the frame received by the micro-controller is all "0" if no fault event is triggered or all "1" if at least one fault has been triggered on the output stage.

Table 14. SDI frame

MSB							LSB
IN7	IN6	IN5	IN4	IN3	IN2	IN1	IN0

Table 15. SDO frame

MSB							LSB
0	0	0	0	0	0	0	0

6.2 Serial data in (SDI)

This pin is the IC input of the serial command frame (MOSI). SDI is reading on CLK rising edges and , thus, the micro-controller must change SDI state during the CLK falling edges.

The bits sent through the SDI line are shifted in the internal Output Status Register. In daisy chaining communication, the micro-controller keeps the $\overline{SS}$ low after the 8th bit to allow the shift of the Output Status Register to the SDO line. The bits in the Output Status Register are frozen by the internal logic when the $\overline{SS}$ goes high.

6.3 Serial data out (SDO)

This pin is the IC output of the serial fault frame (MISO). The information on SDO is updated on CLK falling edges, whereas the micro-controller reads the SDO frame on CLK rising edges, as established by standard. At communication start-up, when the $\overline{SS}$ falling edge is coming, only the first bit of the frame is just available.

SDO pin is tri-stated when the $\overline{SS}$ signal is high.

In daisy chaining communication the SDO line will transfer the content of the internal Output Status Register after the 8th CLK pulse.

6.4 Serial data clock (CLK)

The CLK line is the IC input clock for serial data sampling. SDO is updated on CLK falling edges, and then sampled on the rising edge. The SDI line is sampled on SCK rising edges.

When the $\overline{SS}$ signal is high (slave not selected), the micro-controller should drive the CLK low (settings for MCU SPI port are CPHA = 0 and CPOL = 0).

6.5 Slave select ($\overline{SS}$)

The slave select $\overline{SS}$ signal is used to enable the serial communication shift register. Data is flushed in through the SDI pin and out from the SDO pin only when the $\overline{SS}$ pin is low. On the $\overline{SS}$ pin falling edge, the Fault Register (containing IC fault conditions) is frozen, so any changing on the channel status will be latched until the next $\overline{SS}$ falling edge event, the SDO is enabled and the internal refresh is disabled too. On the $\overline{SS}$ pin rising edge event, the 8 bits in the Output Status Register are frozen and the outputs of the Process Stage are driven accordingly. If more than 8 bits are flushed into the IC, only the last 8 are evaluated, the other ones are flushed out from the SDO pin after fault condition bits. In this way a proper communication is granted in a daisy chain configuration.

Figure 7. **SPI mode diagram**

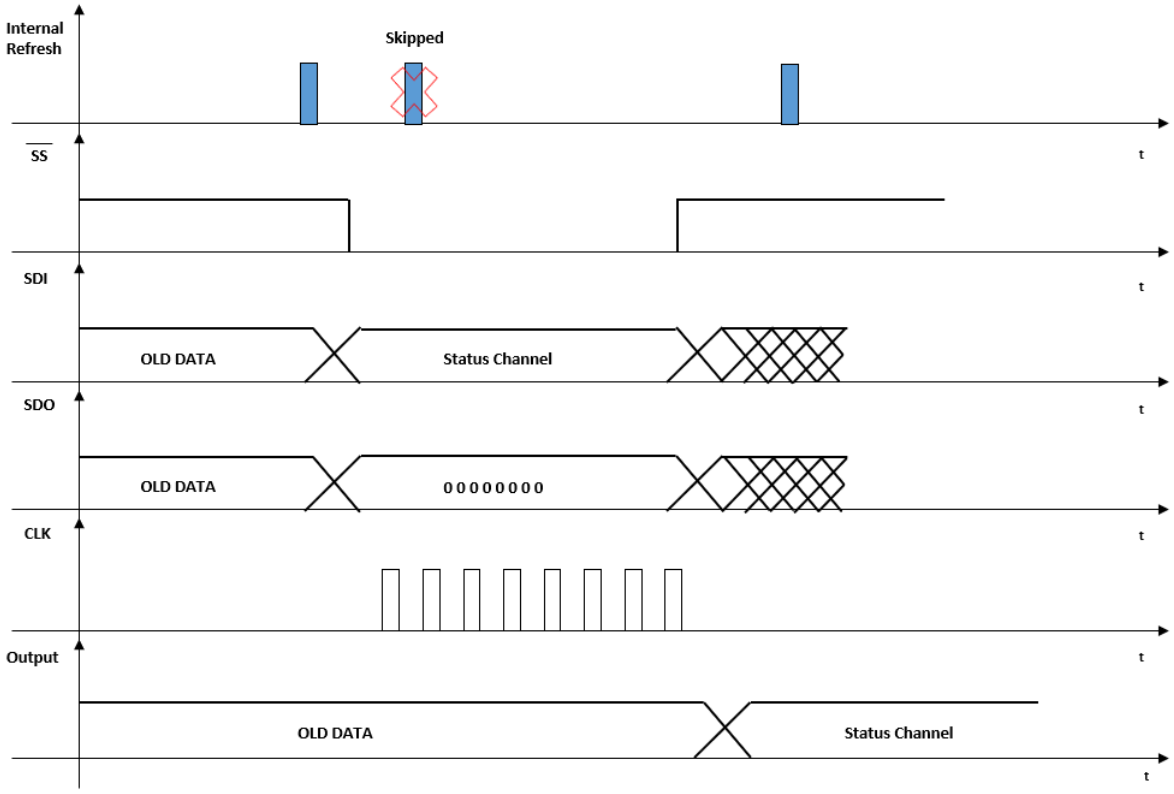


Figure 8. **SPI input timing diagram**

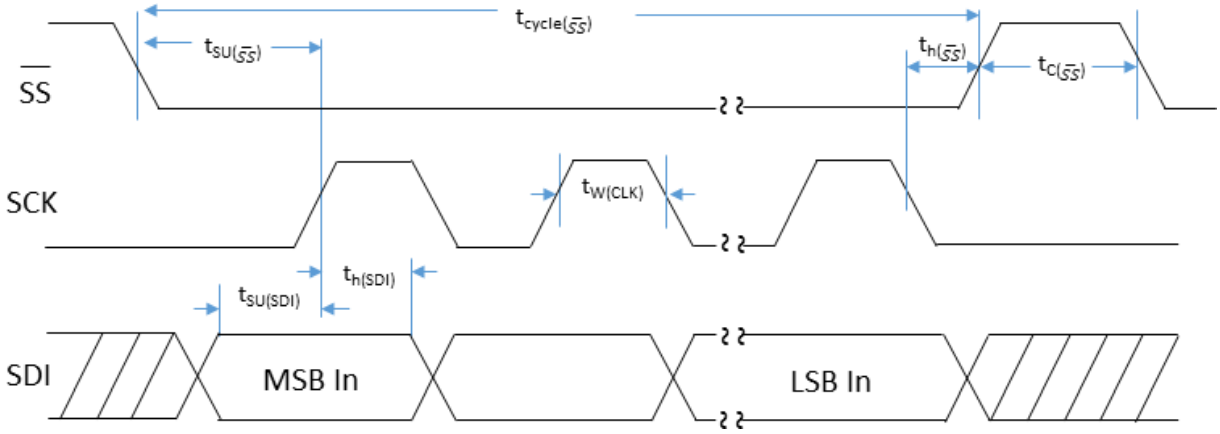
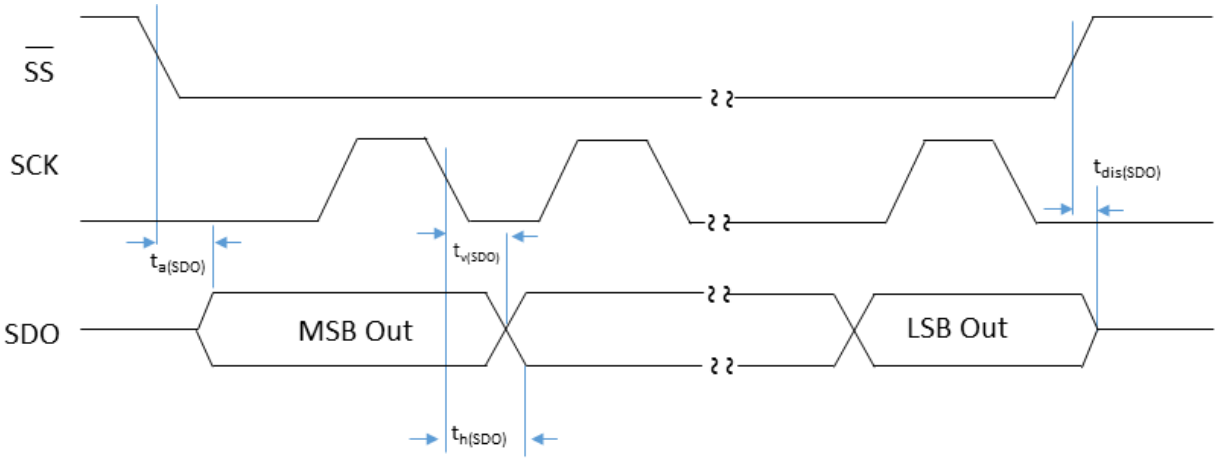


Figure 9. **SPI output timing diagram**



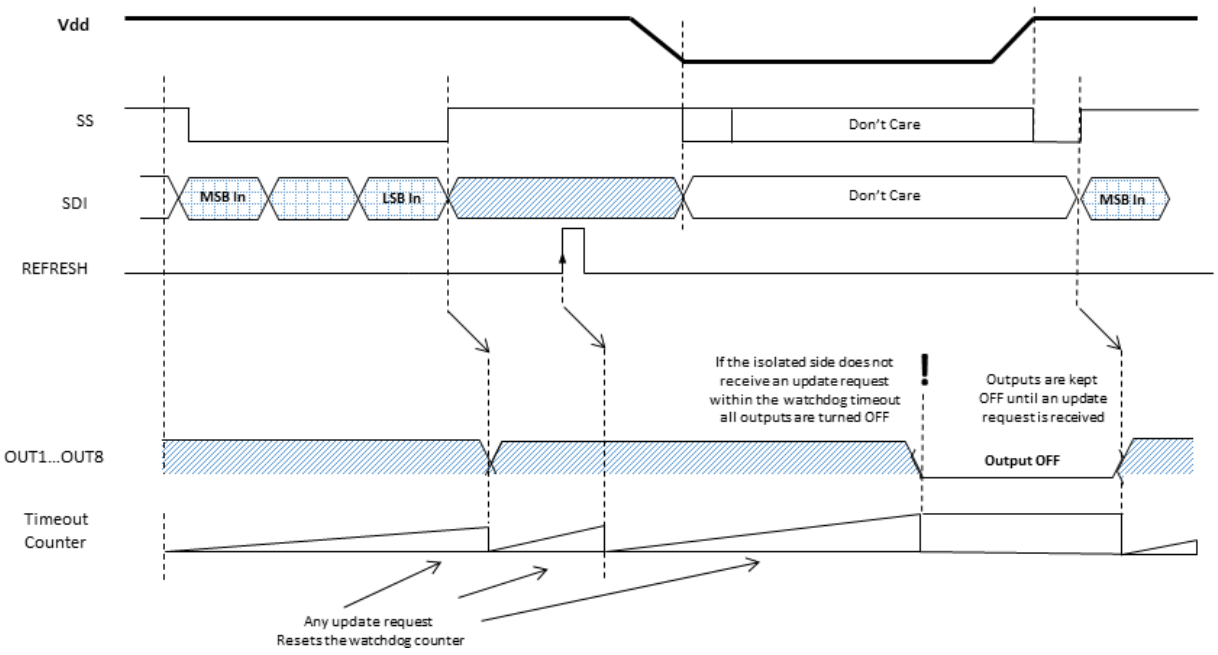
6.5.1 Watchdog

The IC is composed by two chips (Logic Stage and Process Stage) supplied by two independent and galvanic isolated sources (V_{DD}/GND_{DD} and V_{CC}/GND_{CC} pins, respectively).

The IC provides a watchdog function in order to guarantee a safe condition for the Process Stage when V_{DD} (or GND_{DD}) supply voltage is missing. At the end of each SPI communication, the channel status register is transferred to the Process Stage that both reset an internal timeout counter and turns ON/OFF the outputs accordingly. If the Logic Stage does not update the output status within t_{WD}, all the outputs of the Process Stage are disabled until a new update request is received (this also happens if $\overline{SS}$ stays low for longer than t_{WD}).

Independently of the SPI communication, the Logic Stage chip periodically sends a refresh signal to the Process Stage chip. The refresh signal is also considered a valid update signal to reset the timeout counter on the Process Stage, so the isolated side watchdog does not protect the system from a failure of the host controller (e.g., MCU freezing).

Figure 10. **Watchdog behavior**



6.5.2 Output enable (OUT_EN)

This pin provides a fast way to disable all the outputs simultaneously. When the OUT_EN pin is driven low for at least $t_{W(OUT\_EN)}$, all eight outputs are disabled. This timing execution is compatible with an external reset push from the operator, safety requirements, and permits, in a PLC system, a micro-controller polling for obtain all internal information during a reset procedure.

Note that the OUT_EN signal acts as a reset for the internal data register driving the output switches: when the OUT_EN is low, SDO is pulled down and the output stage is forced OFF. To re-enable SDO, it is necessary to raise the OUT_EN pin; to enable the output stage again, it is then necessary to raise the OUT_EN pin and send the desired output configuration by an SPI command.

Figure 11. OUT_EN without effect on output

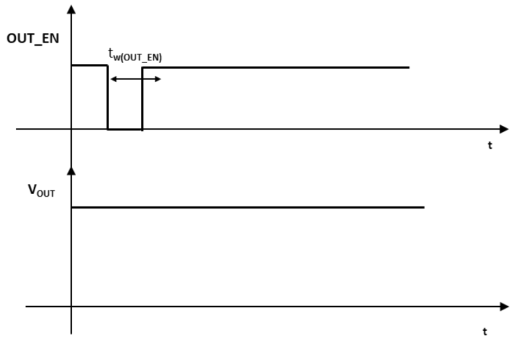
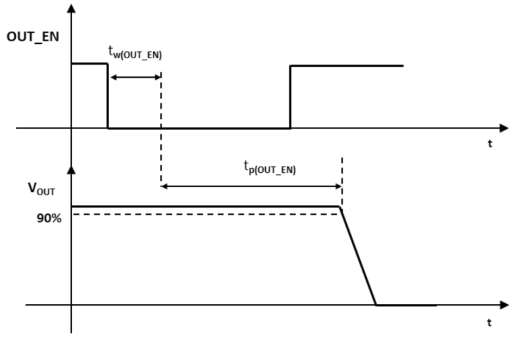


Figure 12. OUT_EN effective on output channel



6.6 FAULT and PGOOD indications

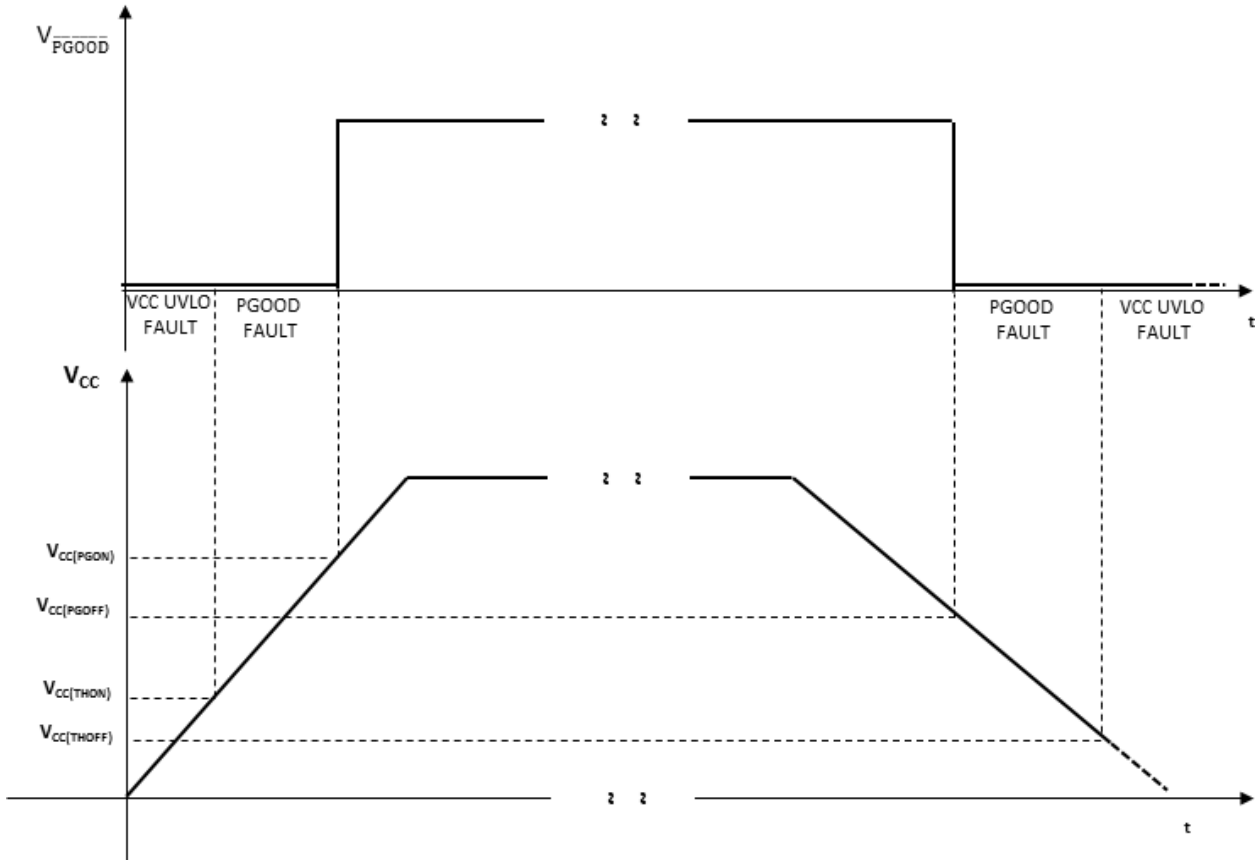
The $\overline{FAULT}$ pin is an active low open drain output indicating fault conditions. This pin is activated when at least one of the following conditions occurs:

- Junction over-temperature ($T_{JX} > T_{JSD}$) of one or more channels of the Process Stage or case shut-down protection (Tc > Tcsd) is active.
- No module-8 SPI communication (the number of bits sent through the SDI is not a multiple of 8)
- Internal communication error. In fact, the IC is able to identify (and report to the micro-controller) if any errors occur in the data transmission between isolation. When it occurs, the output stage maintains the previous ON/OFF status.

The $\overline{PGOOD}$ pin is an active low open drain output indicating if the supply voltage of the Process Stage chip is lower than the internal threshold (see Figure 13).

Note: When $\overline{SS}$ signal is low the transmission between Control Logic Stage and Process Stage is inhibited and the status of $\overline{PGOOD}$ is not refreshed ($\overline{PGOOD}$ refresh time < 120 µs).

Figure 13. **Power GOOD pin behavior**



6.7 Truth table

Table 16. **Truth table**

x = maintain the previous condition.

Condition	Status register BIT_x	OUT_x	Fault register BIT_x	FAULT	PGOOD
Normal operation	1	ON	0	H (not active)	H (not active)
	0	OFF	0		
Thermal Junction ($T_{JX} > T_{JSD}$)	1	OFF	1	L (active)	Don't care
	0	OFF	1	H (not active)	
Thermal Case $T_C > T_{CSD}$	See Figure 21			H (not active)(1)	Don't care
V_{CC} UVLO FAULT (Figure 13)	0	OFF	X	X	L (active)
	1				
POWER GOOD FAULT (Figure 13)	1	ON	Don't care	Don't care	L (active)
	0	OFF			
V_{DD} UVLO (Watchdog)	X	OFF	X	H (not active)	H (not active)
SPI FAULT (module-8 violation)	X	X	Don't care	L (active)	Don't care
Internal communication error	X	X	X	L (active)	Don't care

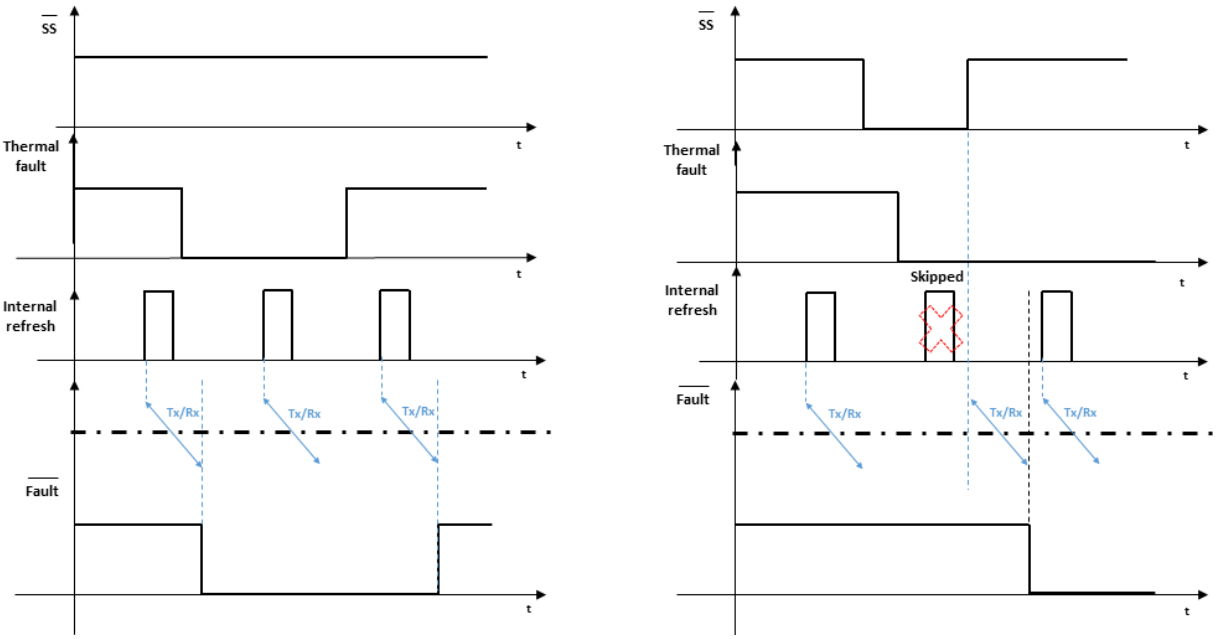
1. *Usually, the thermal case is consequence of thermal junction event latching the FAULT pin low until the thermal junction event resets. If the thermal case is triggered without any thermal junction event (for example in case of very high ambient temperature) then the FAULT pin is not activated*

6.7.1 Junction over-temperature

The thermal status of the device is updated during each transmission sequence between the two isolated stages.

When $\overline{SS}$ is low, the communication between the two stages is disabled. In this case, the thermal status of the device cannot be updated, and the $\overline{FAULT}$ indication could be different to the actual status. In any case, the thermal protections of the channel outputs in the Process Stage are always operative.

Figure 14. Thermal status update



7 Power section

7.1 Current limitation

The current limitation process is activated when the current sense connected on the output stage measures a current value higher than a fixed threshold. When this condition is verified, the gate voltage is modulated to avoid output current increasing over the limitation value.

The following figures (where BIT_X is intended as Xth bit of the Output Status Register) show typical output current waveforms with different load conditions.

Figure 15. Switching on resistive load

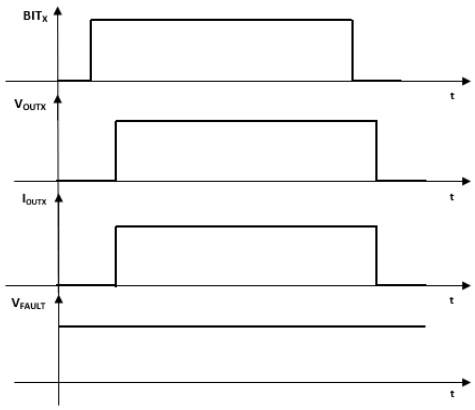


Figure 16. Switching on bulb lamp

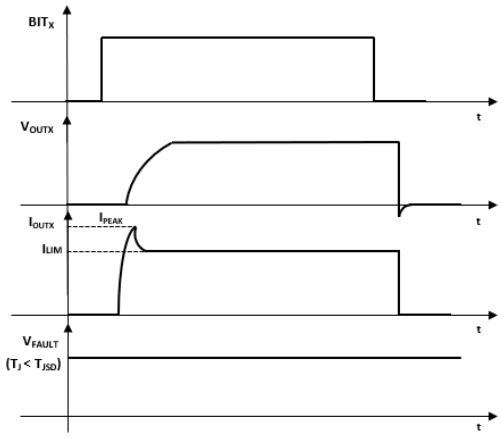


Figure 17. Switching on light inductive load

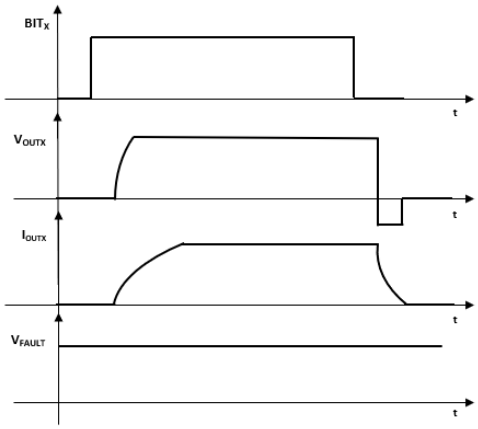


Figure 18. Switching on heavy inductive load

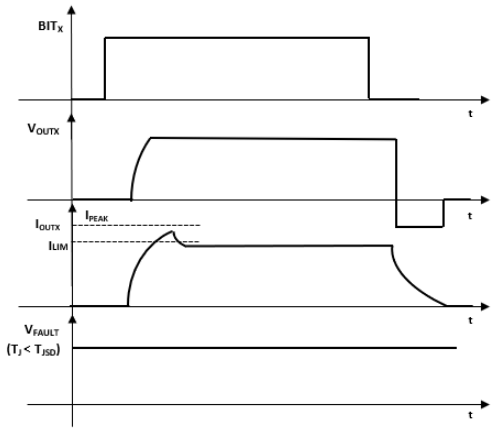


Figure 19. **Short-circuit (with OVT) during ON state**

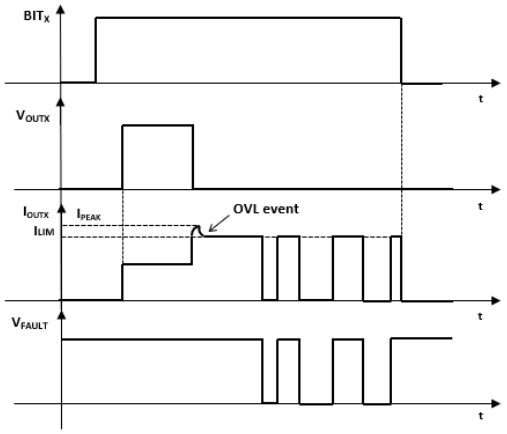
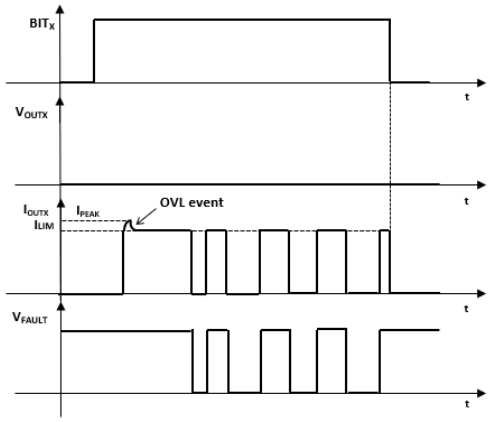


Figure 20. **Switching on short-circuit (with OVT)**



7.2 Thermal protection

The device is protected against overheating due to overload conditions. During driving period, if the output is overloaded, the device suffers two different thermal stresses, the first one related to the junction, and the second related to the case.

The two faults have different trigger thresholds: the junction protection threshold (T_{JSD}) is higher than that of the case protection (T_{CSD}). Generally, the first protection that is activated in thermal stress conditions is the junction thermal shutdown. The output is turned off when the temperature is higher than the related threshold and turned back on when it falls below the reset threshold (T_{JR}). This behavior continues while the fault on the output is present.

If the thermal protection is active and the temperature of the package increases over the fixed case protection threshold, the case protection is activated, and the output is switched off and back on when the junction temperature of each channel in fault and case temperature are below the respective reset thresholds.

Figure 21. **Thermal protection flowchart**

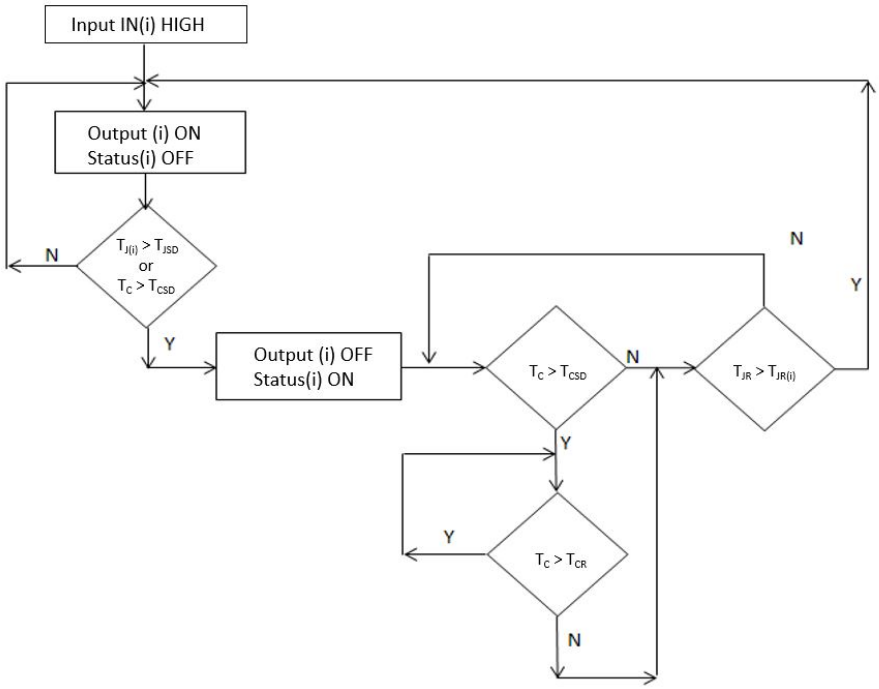


Figure 22. Thermal protection and fault behavior (T_{JSD} triggered before T_{CSD})

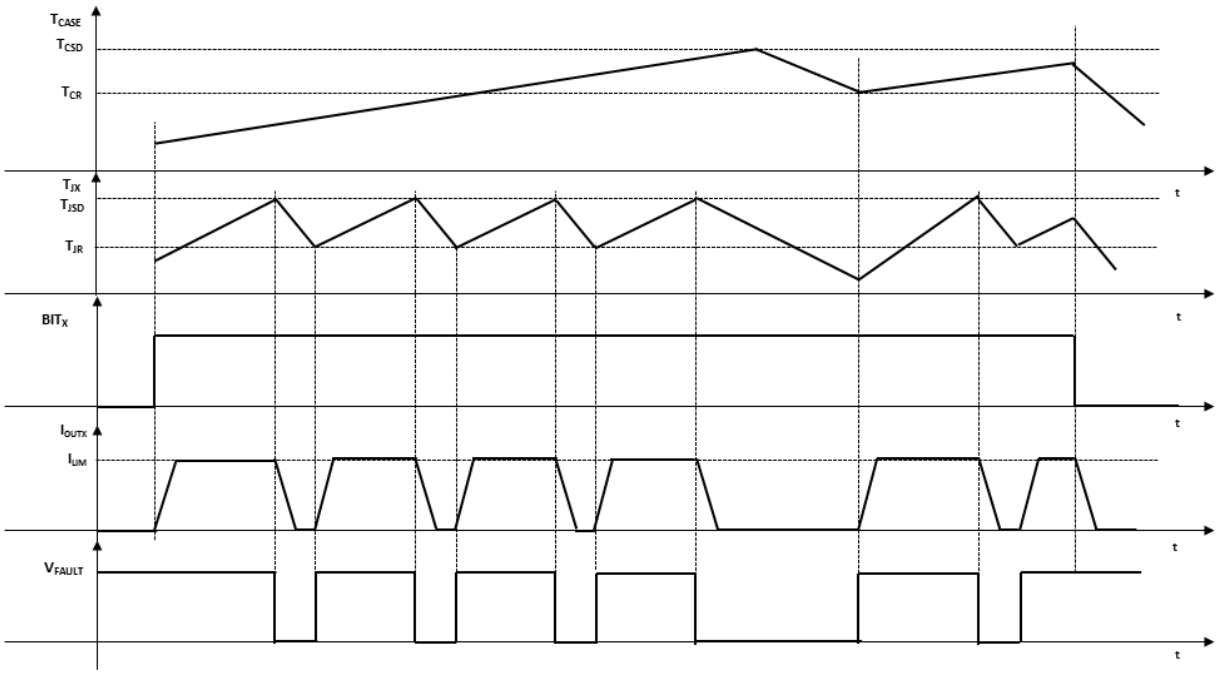
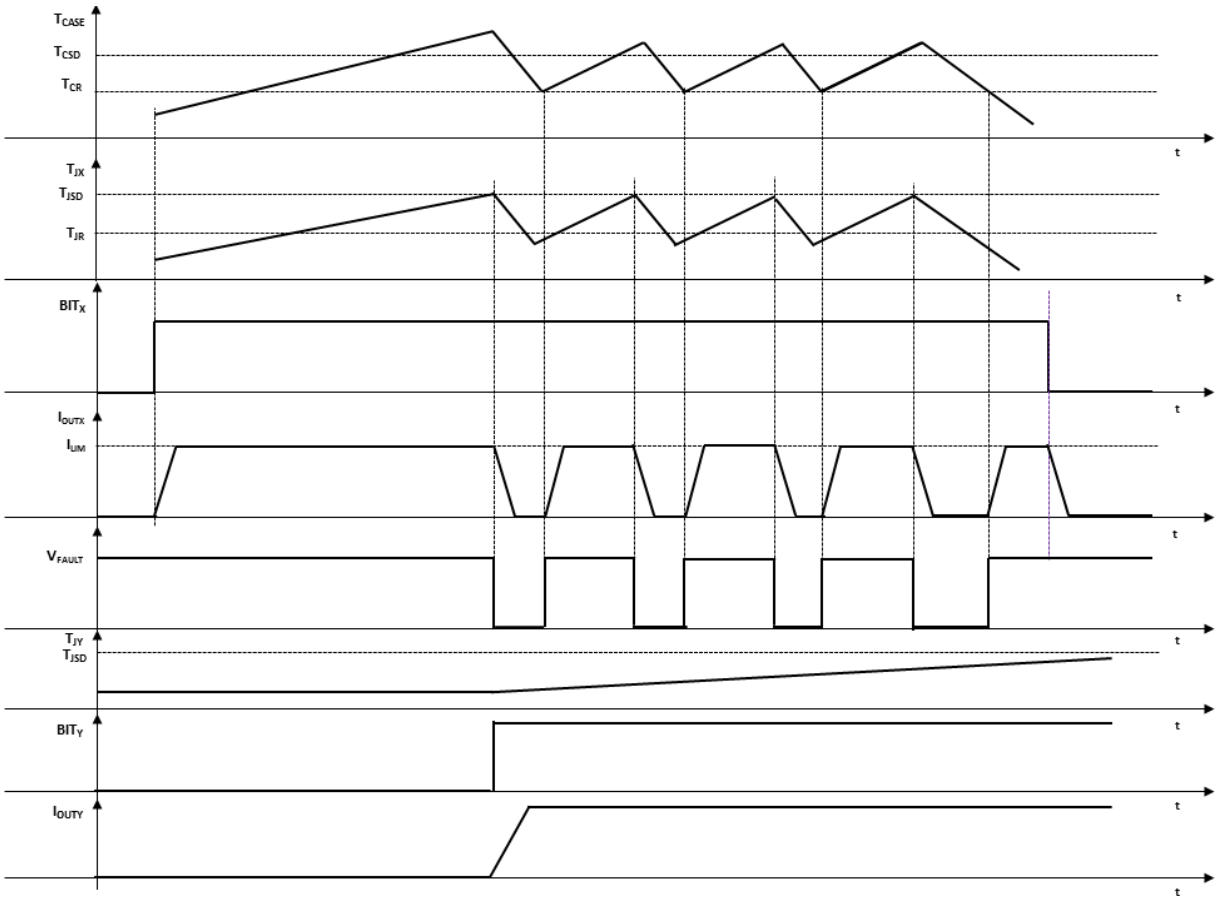


Figure 23. Thermal protection and fault behavior (T_{CSD} triggered before T_{JSD})



8 Reverse polarity protection

Reverse polarity protection can be implemented on board using two different solutions (or both, which is recommended):

1. Placing a resistor (R_{GND}) between IC GND pin and load GND
2. Placing a diode in parallel to a resistor between IC GND pin and load GND

If option 1 is selected, the minimum resistance value must be selected according to the following equation:

$$R_{GND} \geq \frac{V_{CC}}{I_{GND_{CC}}} \quad (1)$$

where $I_{GND_{CC}}$ is the DC reverse ground pin current and can be found in Table 2.

The power dissipated by R_{GND} during reverse polarity is:

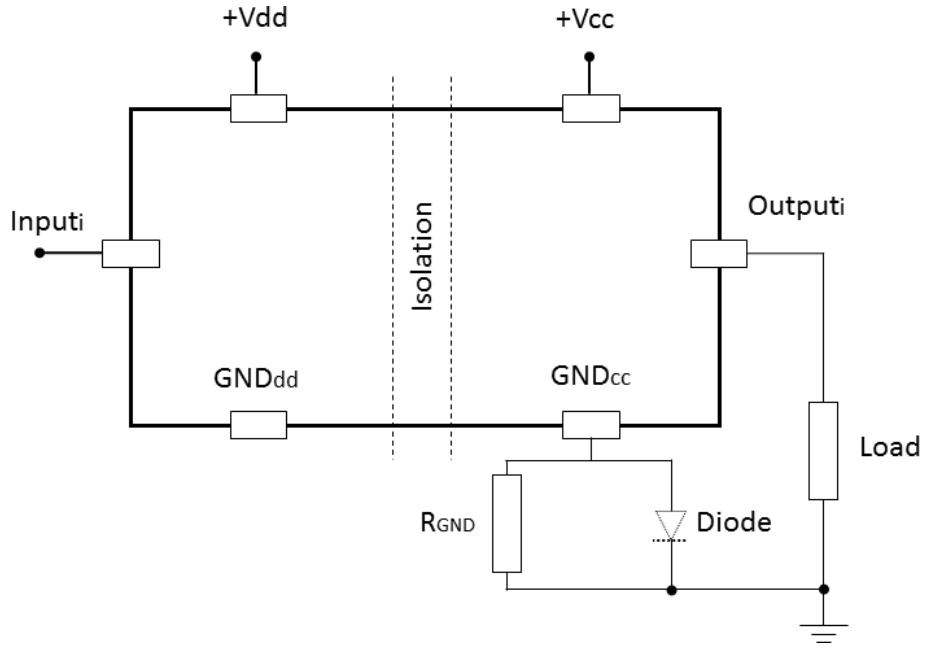
$$P_D = \frac{(V_{CC})^2}{R_{GND}} \quad (2)$$

If option 2 is selected, the diode has to be chosen by taking into account $V_{RRM} > |V_{CC}|$ and its power dissipation capability:

$$P_D \geq I_S \times V_F \quad (3)$$

*Note: In normal operation (no reverse polarity), there is a voltage drop (ΔV) between GND of the device and GND of the system. Using option 1, ΔV = Rgnd * Icc. Using option 2, ΔV = VF@(IF).*

Figure 24. Reverse polarity protection



Note: Input(i) is intended as any input pin on logic side.

This schematic can be used with any type of load.

9 Reverse polarity on VDD

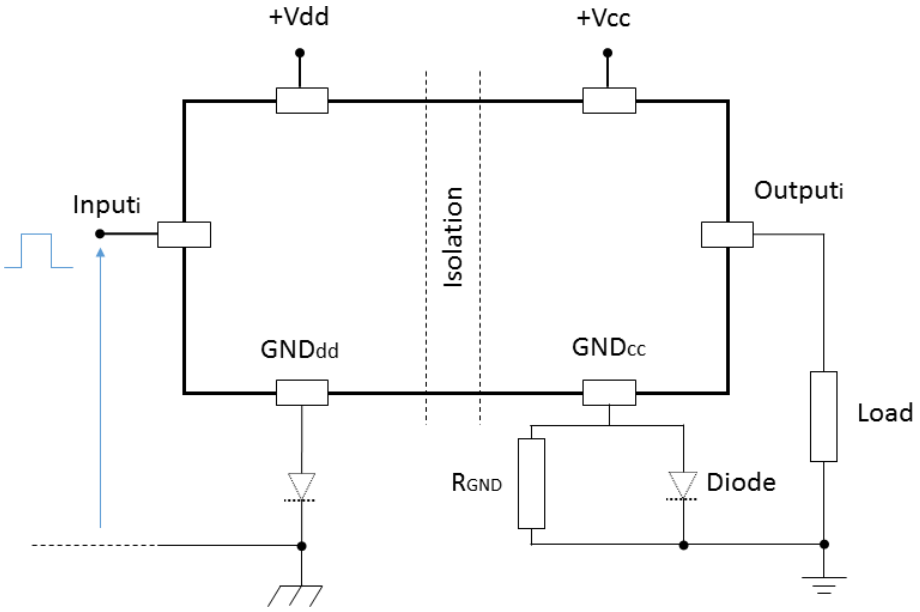
The reverse polarity on V_{DD} can be implemented on board by placing a diode between the GND_{DD} pin and GND digital ground.

The diode must be chosen by taking into account $V_{RRM}>|V_{DD}|$ and its power dissipation capability:

$$P_D \geq I_{DD} \times V_F \quad (4)$$

Note: In normal operation (no reverse polarity), there is a voltage drop (ΔV = VF@(Idd)) between GND_{DD} of the device and digital ground of the system. In order to guarantee to proper
triggering of the input signal, ΔV(max.) must result lower than $V_{IH(MIN)}$.

Figure 25. V_{DD} reverse polarity protection



Note: Input(i) is intended as any input pin on logic side.

10 Demagnetization energy

Figure 26. **Single pulse demagnetization energy vs. load current (Typical values at T_{AMB} = 125 °C)**

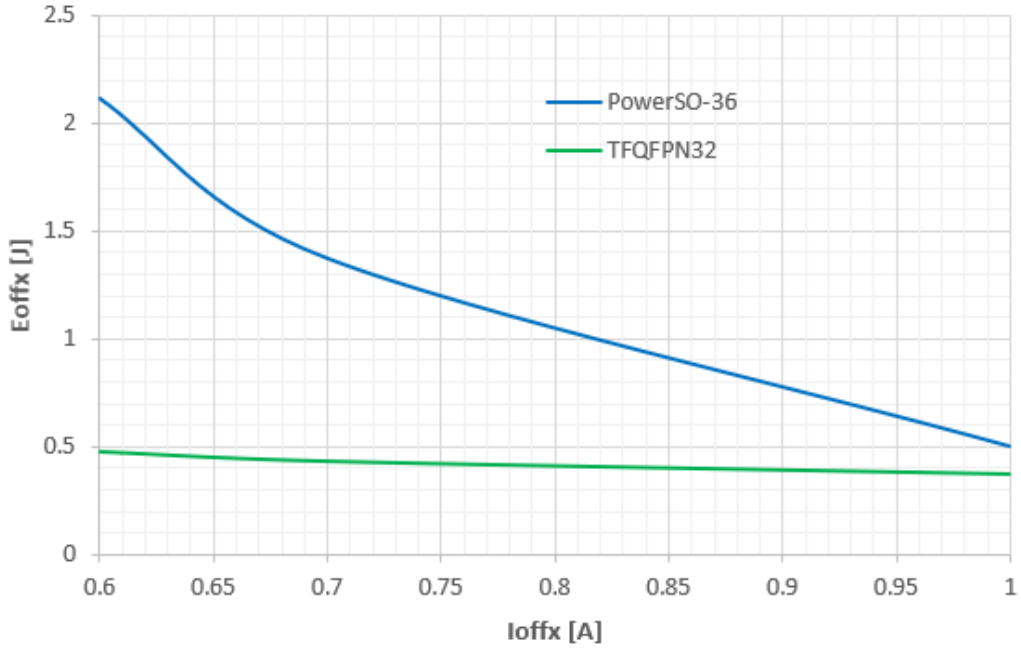


Figure 26 shows the single pulse (not repetitive) demagnetization capability per channel, all channels switched simultaneously

Figure 27. **Single pulse inductive load capability vs. load current (T_{AMB} = 125 °C)**

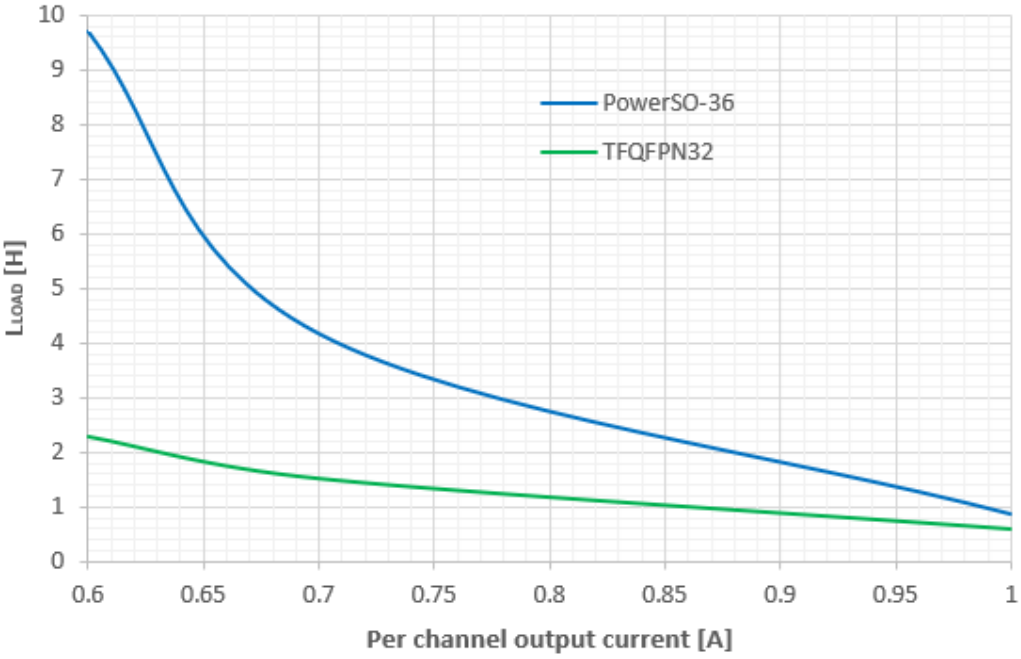
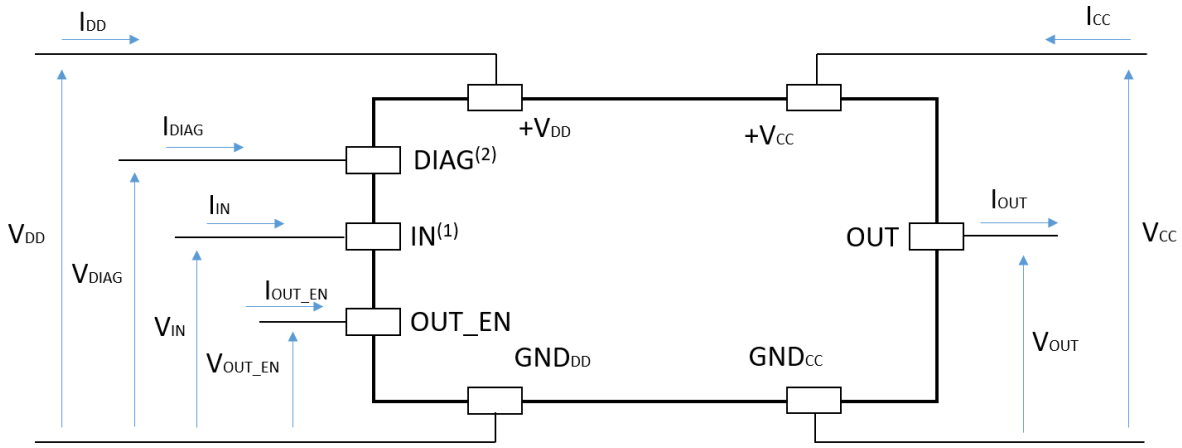


Figure 27 shows the single pulse (not repetitive) inductive load capability per channel, all channels switched simultaneously

11 Conventions

11.1 Supply voltage and power output conventions

Figure 28. **Supply voltage and power output conventions**

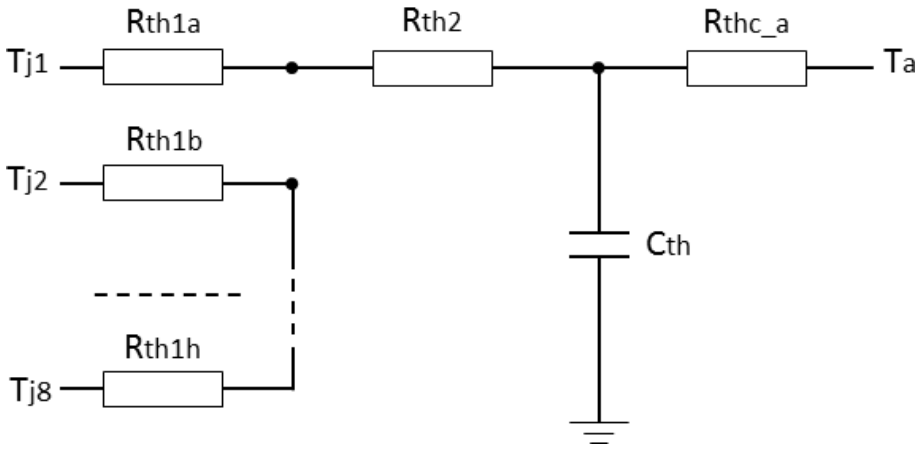


(1): intended as any input pin on logic side
(2): intended as any open drain pin on logic side

12 Thermal information

12.1 Thermal impedance

Figure 29. **Simplified thermal model of the process stage**

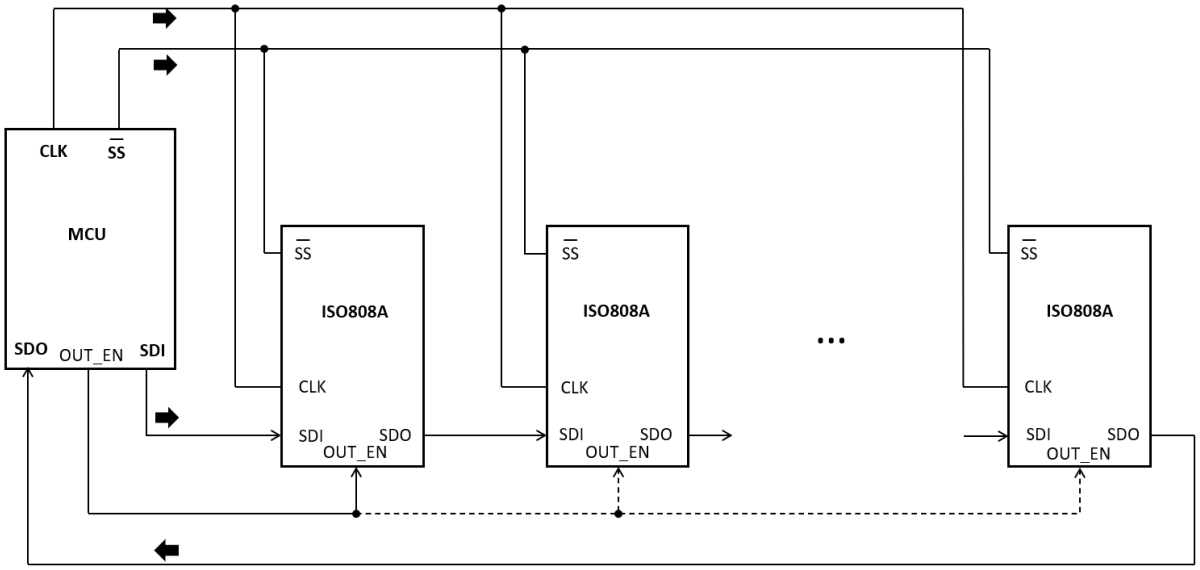


13 Daisy chaining

The ISO808A can be daisy-chained by connecting the MOSI port of the microcontroller to the SDI pin of the first IC of the chain; the SDO pin of the first IC of the chain to the SDI pin of the second (and similarly for the next ICs of chain); the SDO pin of the last IC of the chain to the MISO port of the microcontroller.

The $t_{cycle(SS)}$ (see Figure 8) must take into account the internal communication timing ($f_{refresh}$ and t_{WD}): it is recommended $t_{cycle(SS)}$ (max.) < 136 µs. The maximum number of ICs that can be daisy chained depends on the SPI clock frequency set by the microcontroller.

Figure 30. Example of daisy-chaining connection



14 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

14.1 PowerSO-36 package information

Figure 31. PowerSO-36 package outline

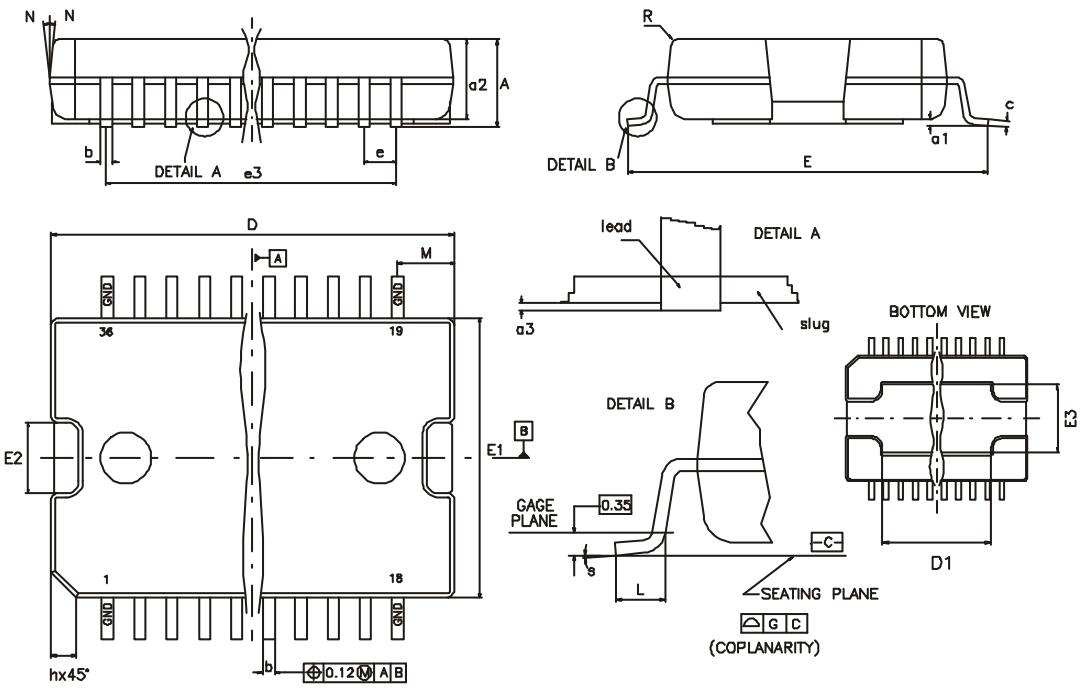


Table 17. PowerSO-36 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			3.6
a1	0.10		0.30
a2			3.30
b	0.22		0.38
c	0.23		0.32
D(1)	15.80		16.00
D1	9.40		9.80
E	13.90		14.50
E1(1)	10.90		11.10
E2			2.90
E3	5.80		6.20
e		0.65	
e3		11.05	
G	0		0.10
H	15.50		15.90
h			1.10
L	0.80		1.10
N			10°
S	0°		8°

1. *"D" and "E1" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm (0.006"). Critical dimensions are "a3", "E" and "G"*

Figure 32. **PowerSO-36 suggested footprint**

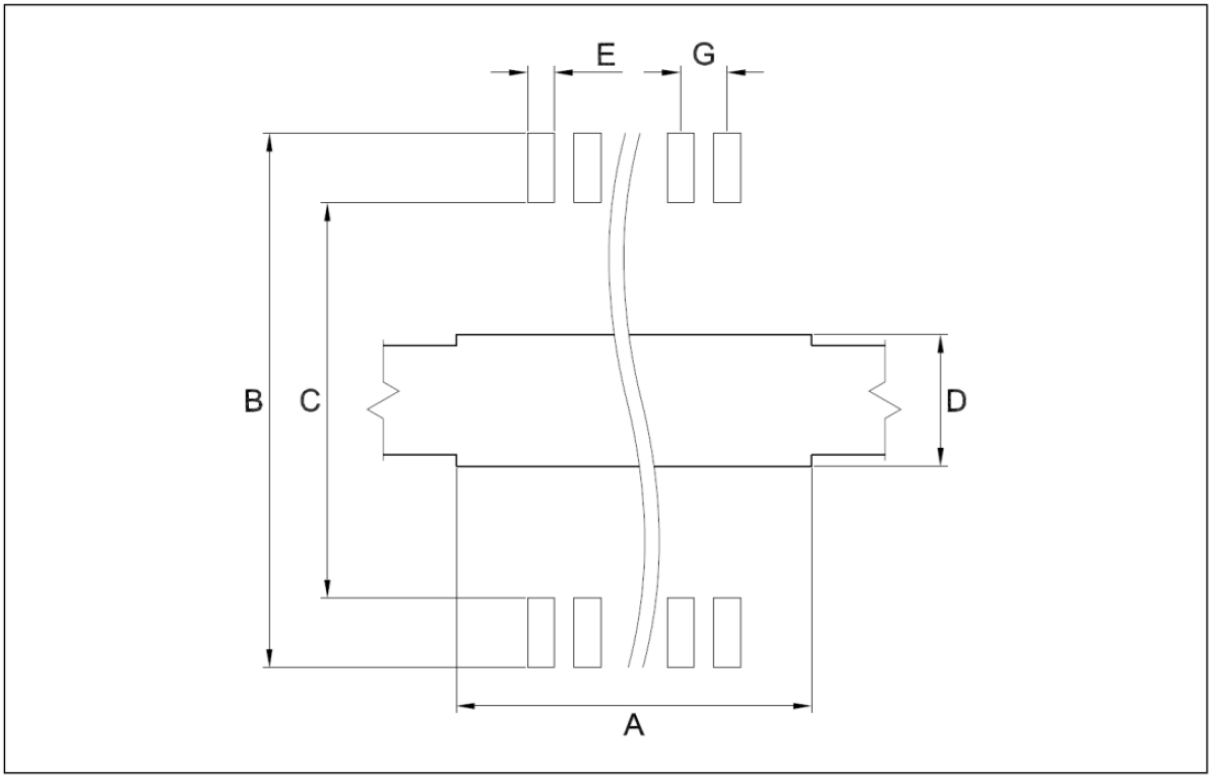


Table 18. **PowerSO-36 footprint data**

Dim	mm
A	9.5
B	14.7-15.0
C	12.5-12.7
D	6.3
E	0.42
G	0.65

14.2 TFQFPN32 package information

Figure 33. **TFQFPN32 package outline**

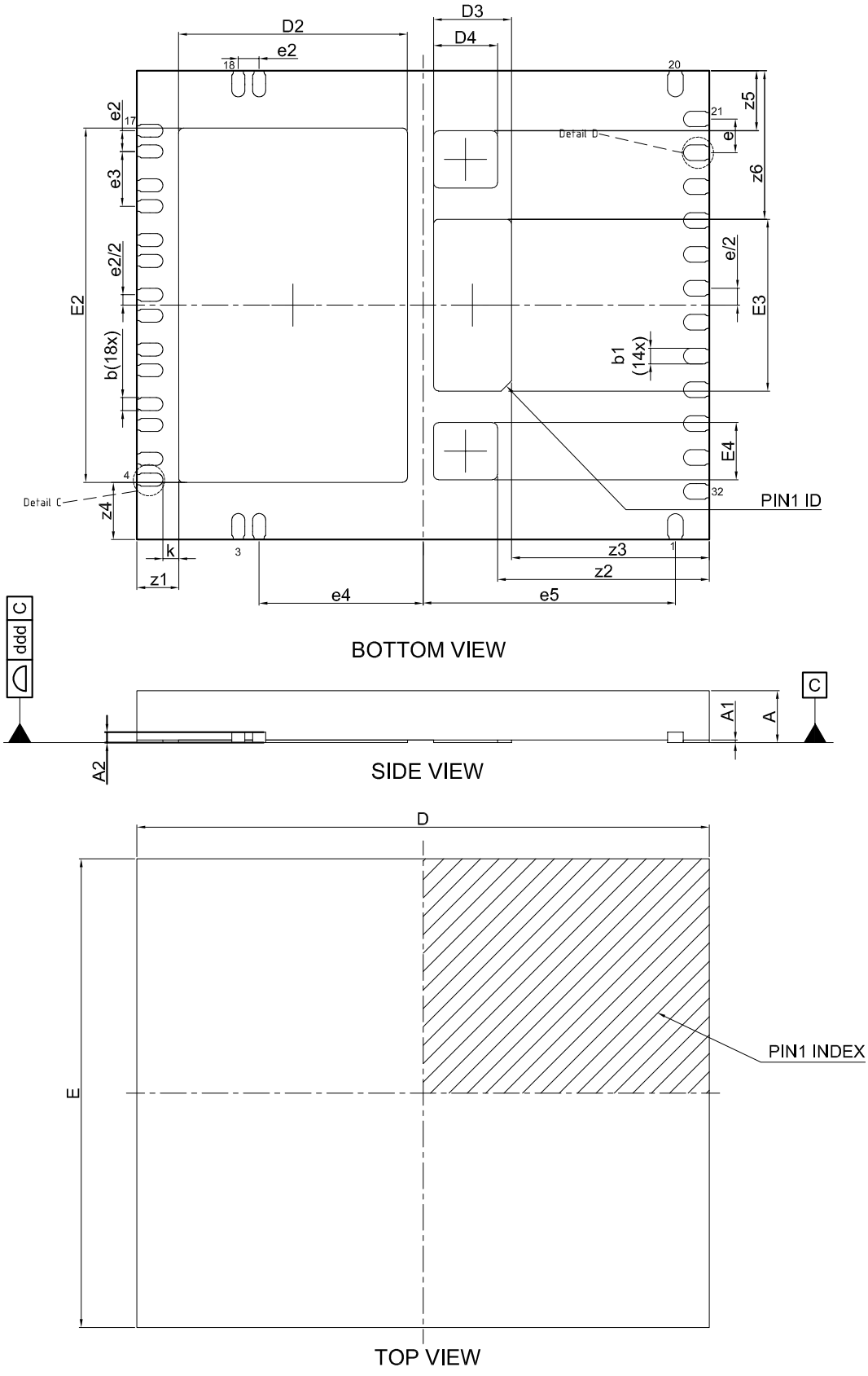


Figure 34. TFQFPN32 package detail outline

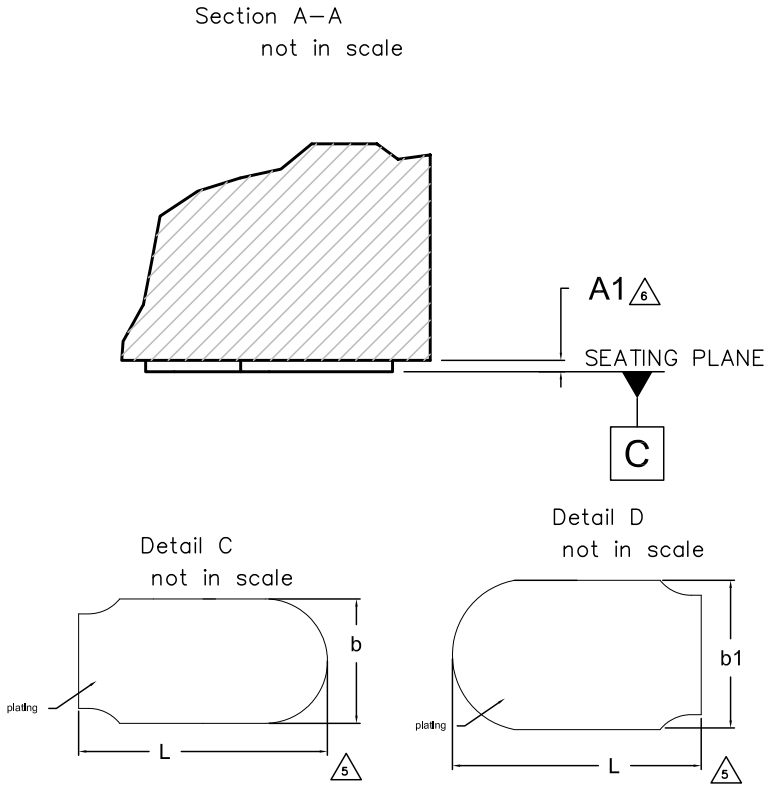


Figure 35. TFQFPN32 suggested footprint (measured in mm)

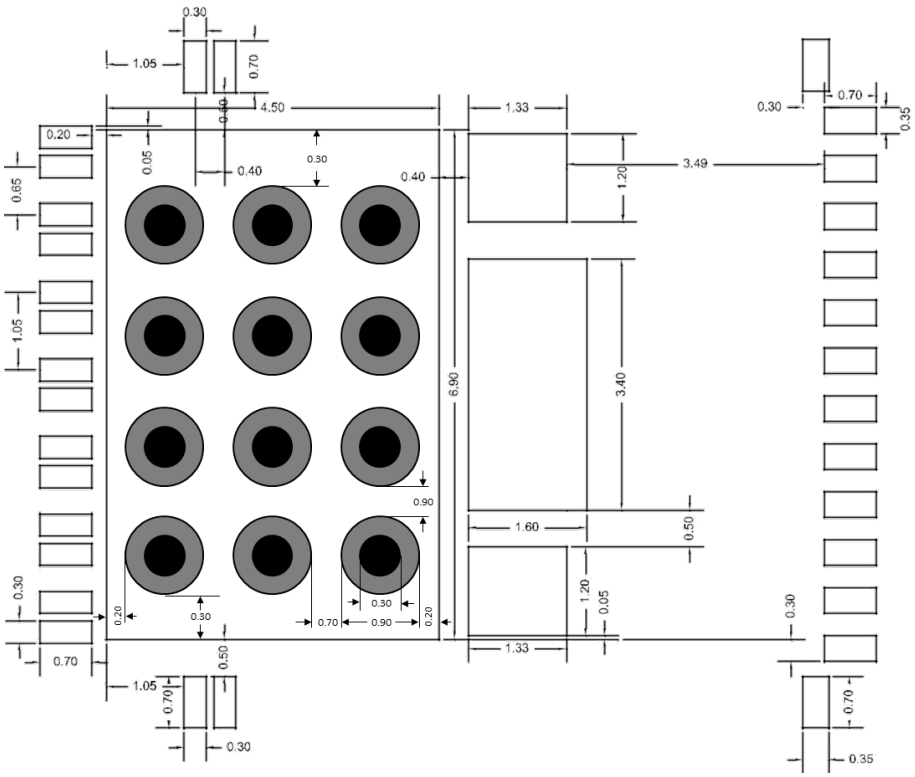


Table 19. TFQFPN32 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.95	1.00	1.05
A1	0	-	0.05
A2	-	0.20 REF	-
b (1)	0.20	0.25	0.30
b1(1)	0.25	0.30	0.35
D	10.90	11.0	11.10
E(1)	8.90	9.00	9.10
D2	4.30	4.40	4.50
E2	6.70	6.80	6.90
D3	1.40	1.50	1.60
E3	3.20	3.30	3.40
D4	1.13	1.23	1.33
E4	1.00	1.10	1.20
e	-	0.65	-
e2	-	0.40	-
e3	-	1.05	-
e4	-	3.15	-
e5	-	4.85	-
k	0	0.30	-
z1	-	0.80	-
z2	-	4.07	-
z3	-	3.80	-
z4	-	1.10	-
z5	-	1.15	-
z6	-	2.85	-
L(1)	0.45	0.50	0.55

1. *Dimensions “b” and “L” are measured on terminal plating surface.*

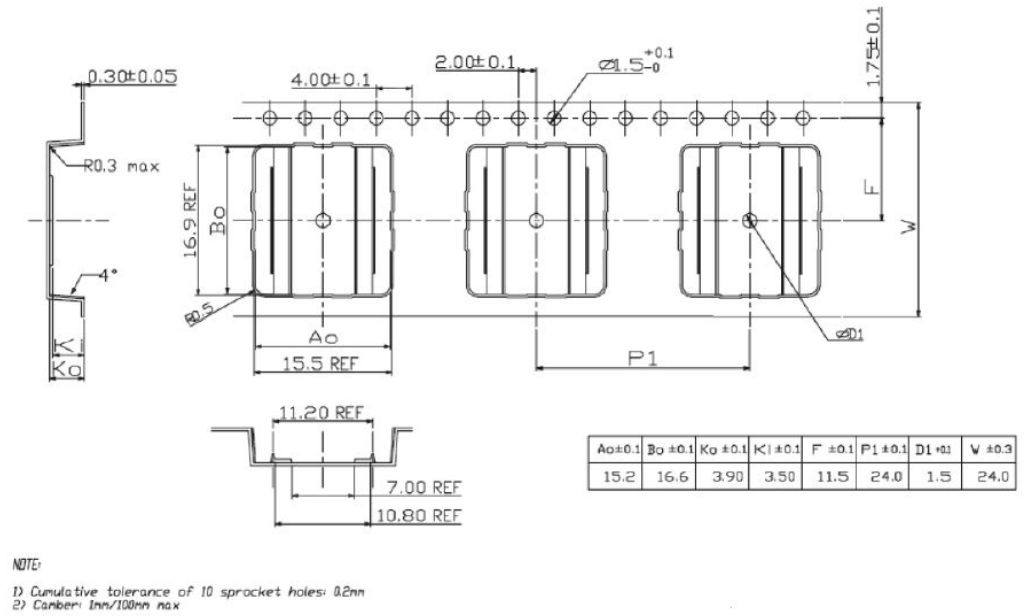
Table 20. Tolerance of form and position

Symbol	Tolerance of form and position	Definition	Notes
Aaa	0.15	The bilateral profile tolerance that controls the position of the plastic body sides. The centers of the profile zones are defined by the basic dimensions D and E.	-
Bbb	0.10	The tolerance that controls the position of the entire terminal pattern with respect to datums A and B. The center of the tolerance zone for each terminal is defined by the basic dimension "e" as related to datum's A and B.	-
Ccc	0.10	The tolerance located parallel to the seating plane in which the top surface of the package must be located.	-
ddd	0.08	The tolerance that controls the position of the terminals to each other. The centers of the profile zones are defined by basic dimension "e".	This tolerance is normally compounded with tolerance zone defined by bbb.
eee	0.08	The unilateral tolerance located above the seating plane where in the bottom surface of all terminals must be located.	This tolerance is commonly known as the "coplanarity" of the package terminals.
fff	0.10	Thetolerance that controls the position of the exposed metal heat feature. The center of the tolerance zone will be datum's defined by the centerlines of the package body.	-
REF	-	-	No tolerance for A2

15 Packing information

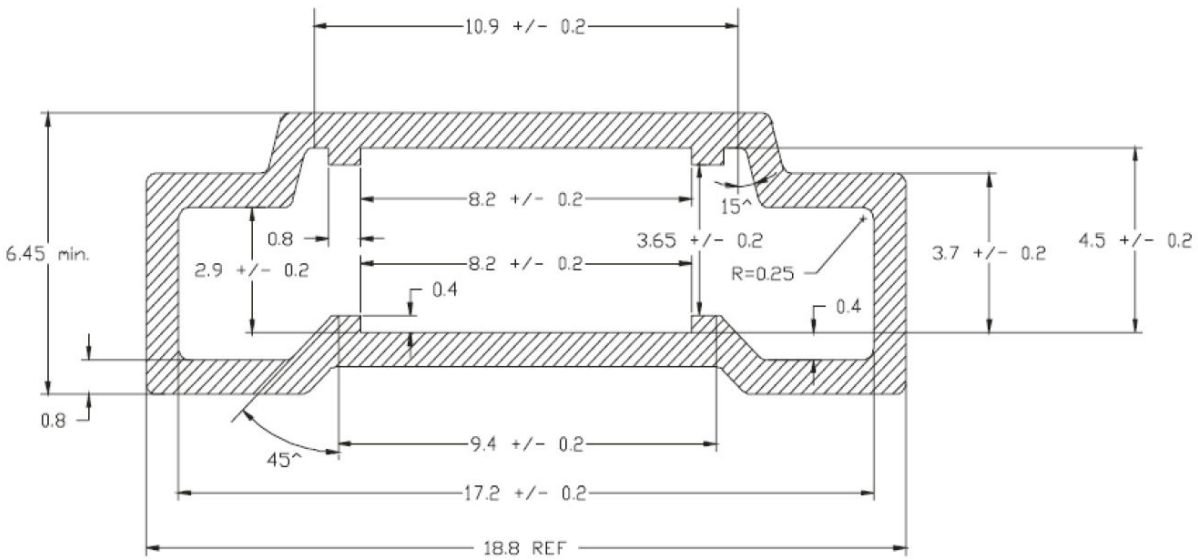
15.1 PowerSO-36 packing information

Figure 36. **PowerSO-36 carrier tape**



Ao±0.1	Bo ±0.1	Ko ±0.1	K ±0.1	F ±0.1	P1 ±0.1	D1 +01	W ±0.3
15.2	16.6	3.90	3.50	11.5	24.0	1.5	24.0

Figure 37. **PowerSO-36 shipping tube**



15.2 TFQFPN32 packing information

Figure 38. **Tape and reel packing method concept**

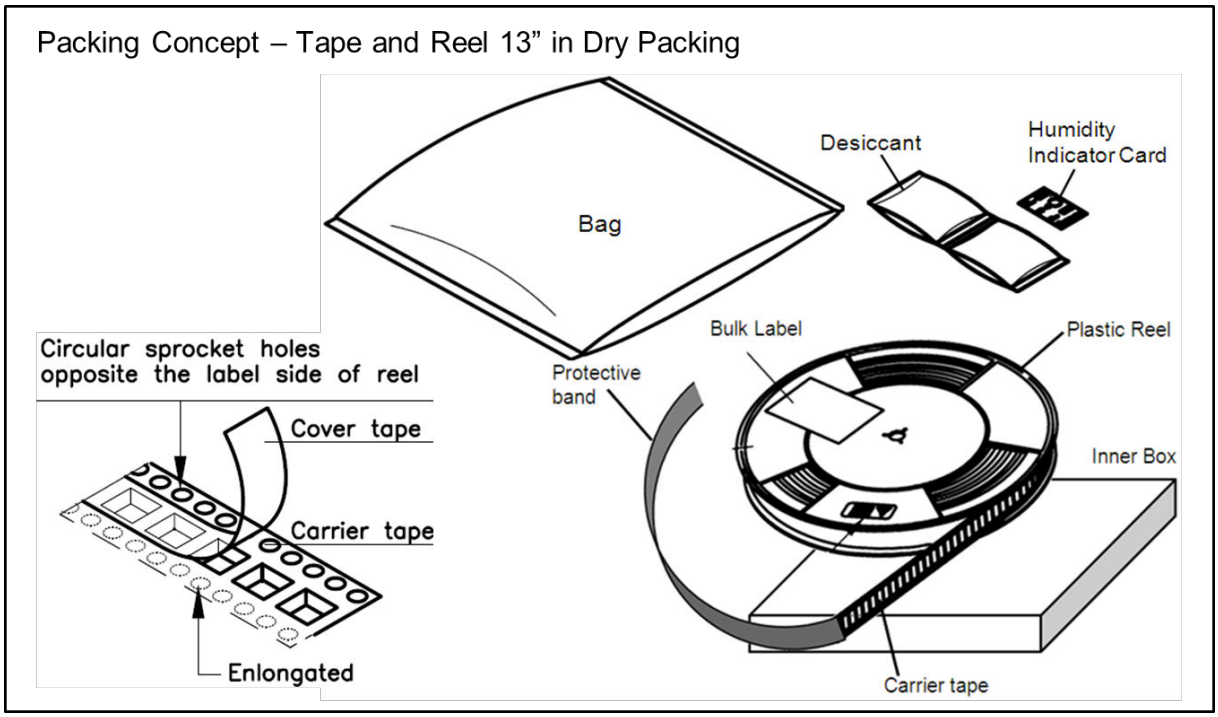


Figure 39. **Winding direction**

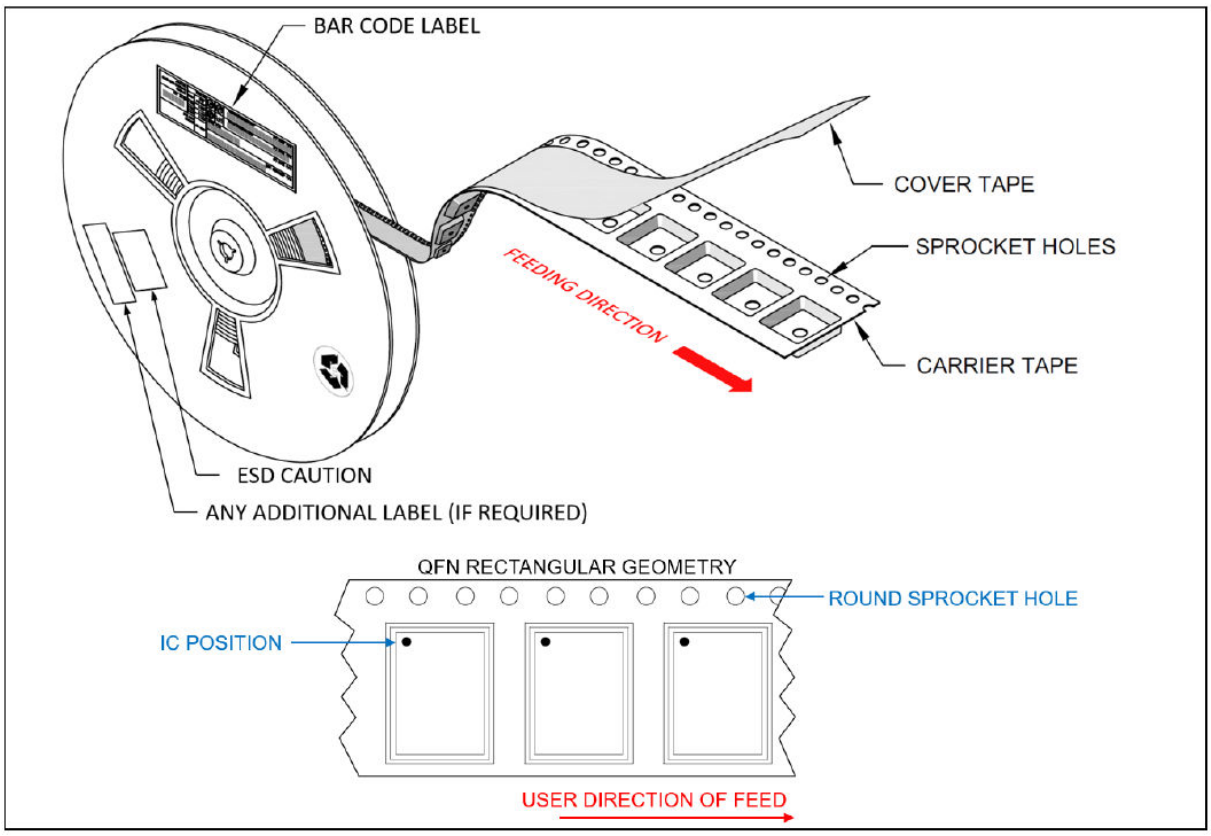
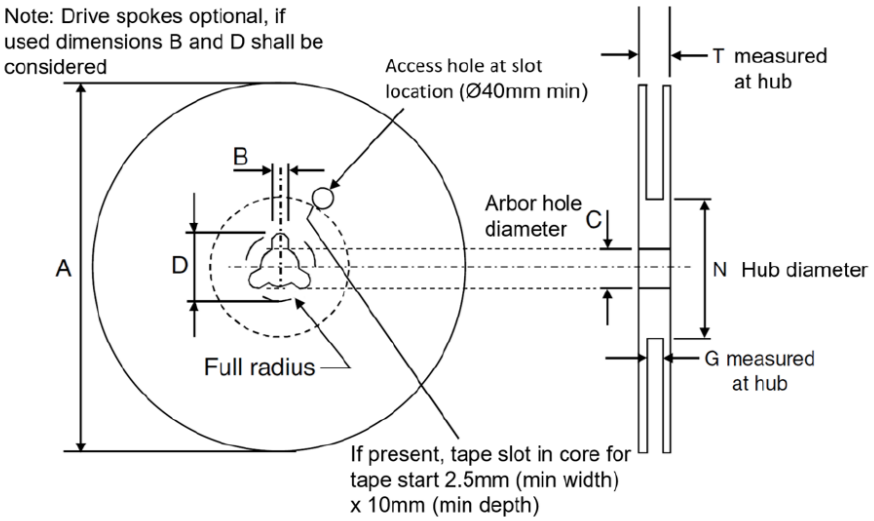
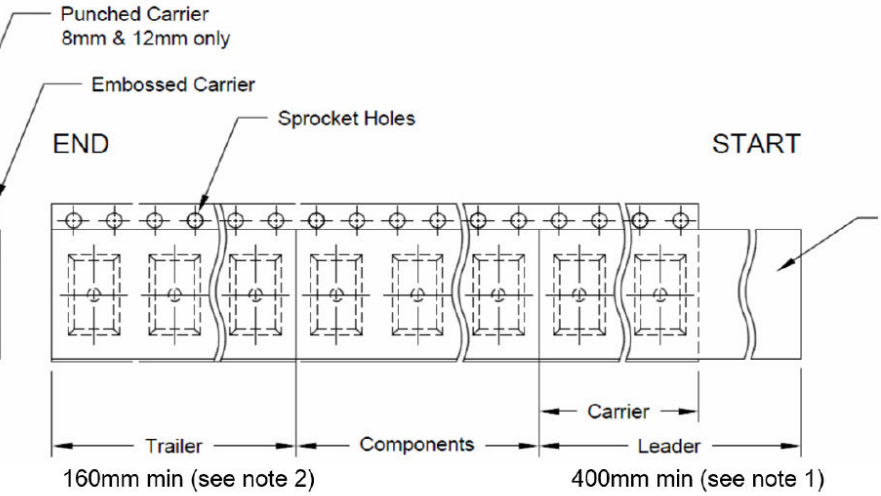


Figure 40. **Reel dimensions (as per EIA-481 specification)**



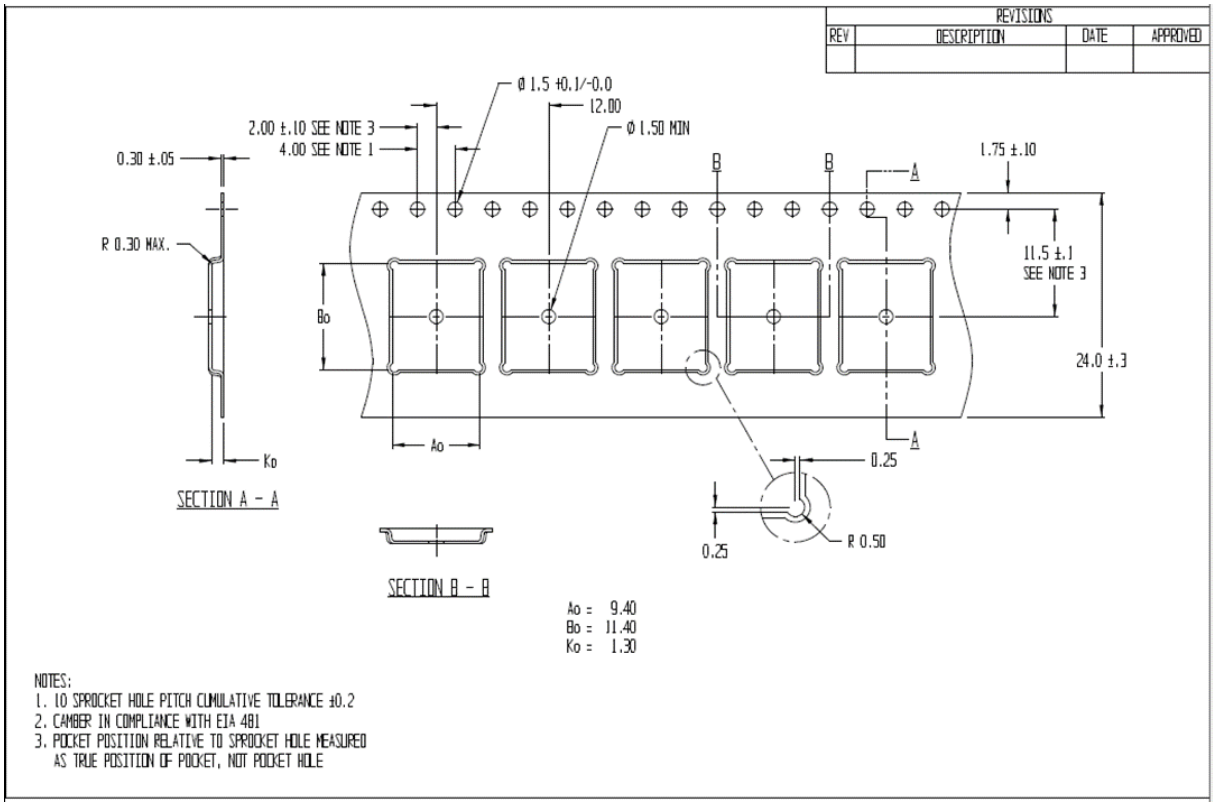
Tape width (mm)	(A) max Reel diameter (mm)	(B) min (mm)	(C) Center hole diameter (mm)	(D) min (mm)	(G) Reel thickness (mm)	(N) min Hub diameter (mm)	(T) max Total thickness (mm)
24	330 ± 2.0	1.5	13 + 0.5 -0.2	20.2	24.4 ± 2.0	100 ± 2.0	30.4

Figure 41. **Leader and Trailer dimensions (as per EIA-481 specification)**



1. There shall be a leader of 400 mm minimum of cover tape, which includes at least 100 mm of carrier tape with empty compartments and sealed by the cover tape. All of the leader may consist of the carrier tape with empty compartments sealed by cover tape.
2. There shall be a trailer of 160 mm minimum of empty carrier tape sealed with cover tape. The entire carrier tape must release from the reel hub as the last portion of the tape unwinds from the reel without damage to the carrier tape and the remaining components in the cavities.

Figure 42. **TFQFPN32 carrier tape**



16 Ordering information

Table 21. **Ordering information**

Part number	Package	Packaging
ISO808A	PowerSO-36	Tube
ISO808A-1	PowerSO-36	Tube
ISO808ATR	PowerSO-36	Tape and reel
ISO808ATR-1	PowerSO-36	Tape and reel
ISO808AQTR	TFQFPN32	Tape and reel
ISO808AQTR-1	TFQFPN32	Tape and reel

Revision history

Table 22. **Document revision history**

Date	Revision	Changes
21-Dec-2022	1	Initial release.
12-Sep-2023	2	Throughout the document added reference to TFQFPN32 package: changed Section ISO808A cover image ; updated table in Section Product status link / summary; updated Section Features with ISO808AQ/ ISO808AQ-1; updated first row in Section Description; added Figure 3; updated Table 1; updated Table 2; updated Table 3; updated Table 6, Table 11 and Table 12; updated Figure 15, Figure 16, Figure 17, Figure 18, Figure 19, Figure 20, Figure 22, Figure 23 and Figure 26; added Figure 27; added Section 14.2 and Section 15.2; updated Table 21

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